

Positron Annihilation Spectroscopy for vacancy defects studies in irradiated tungsten: Combination of modelling and experiments for vacancy size distribution and impurities interaction determination

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MoD-PMI 2025, Vienna, 26-28/05/2025

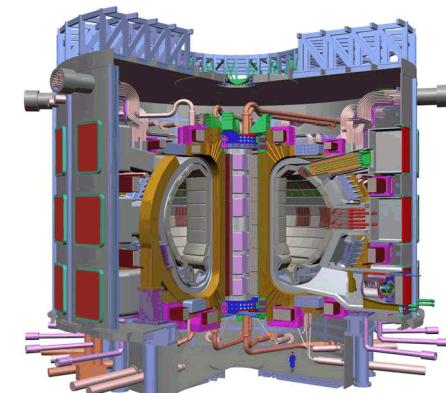
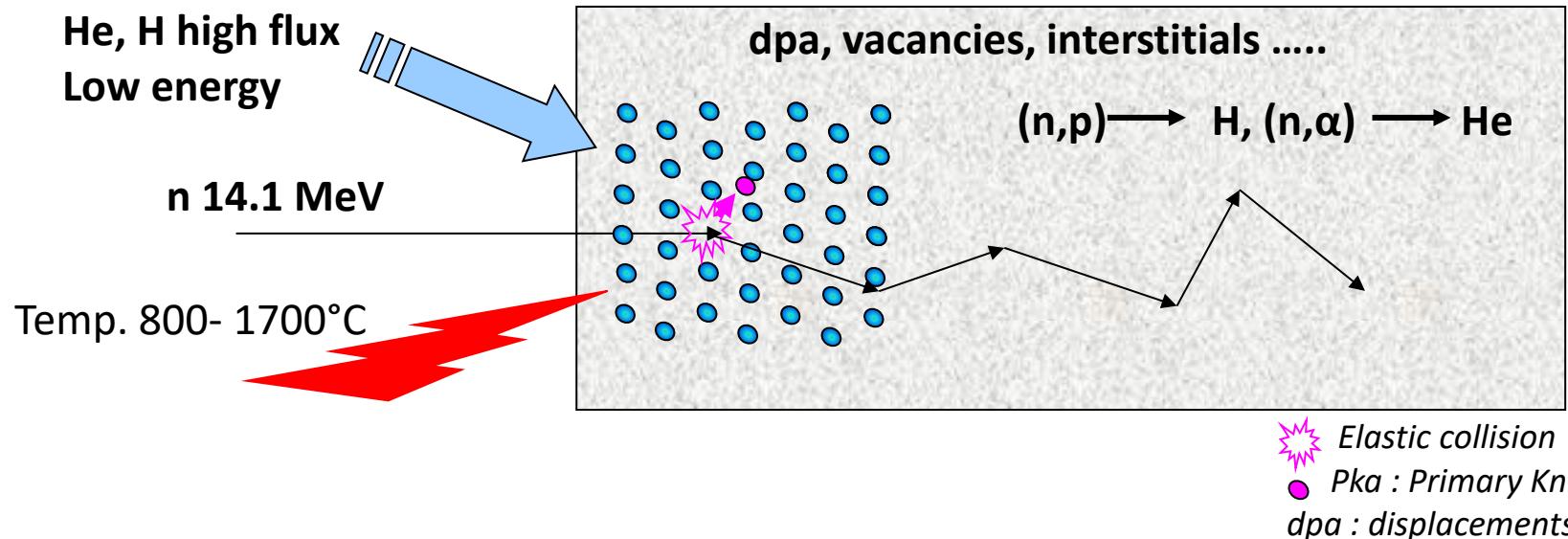


✓ ITER, DEMO : very hard conditions for materials

✓ Fusion reaction



Plasma and neutrons irradiations

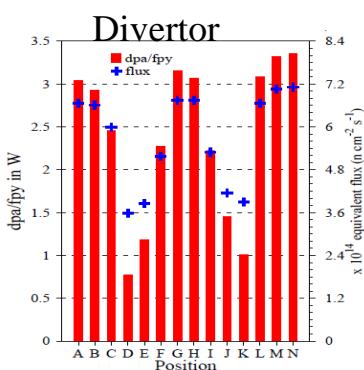
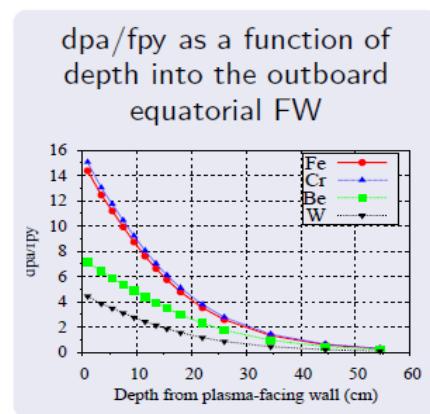
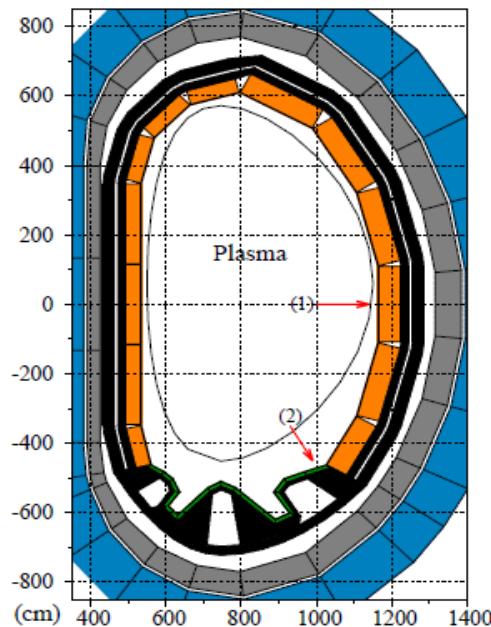


ITER Tokamak

Big challenges : for thermal, electrical and mechanical properties

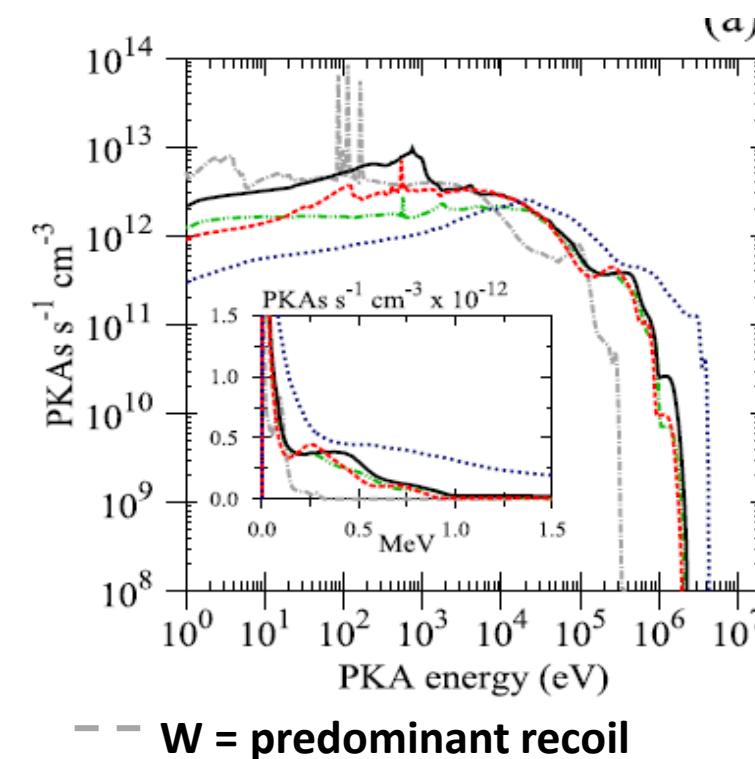
Tungsten divertor and first wall (ITER), first wall? (DEMO)

Calculations in DEMO

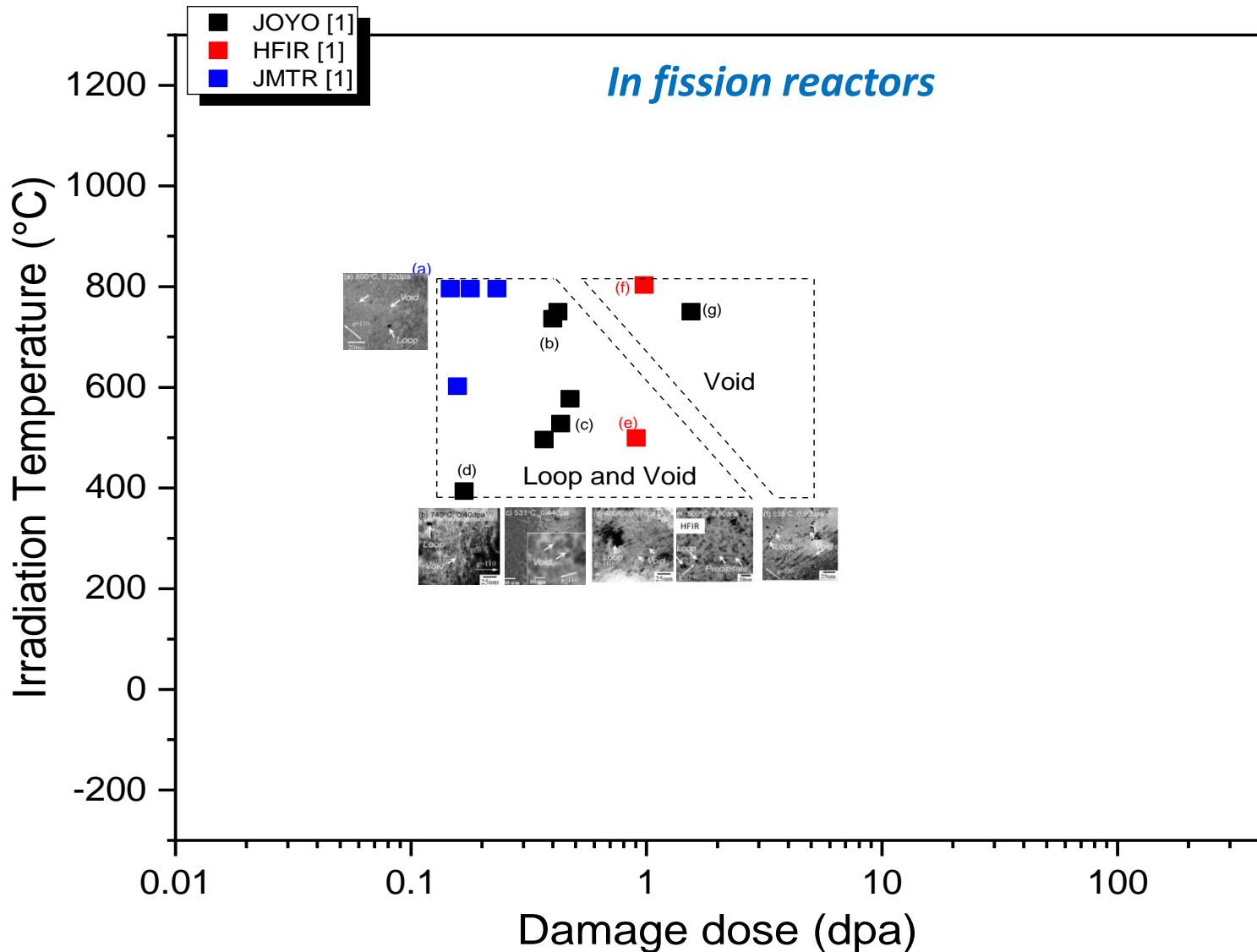


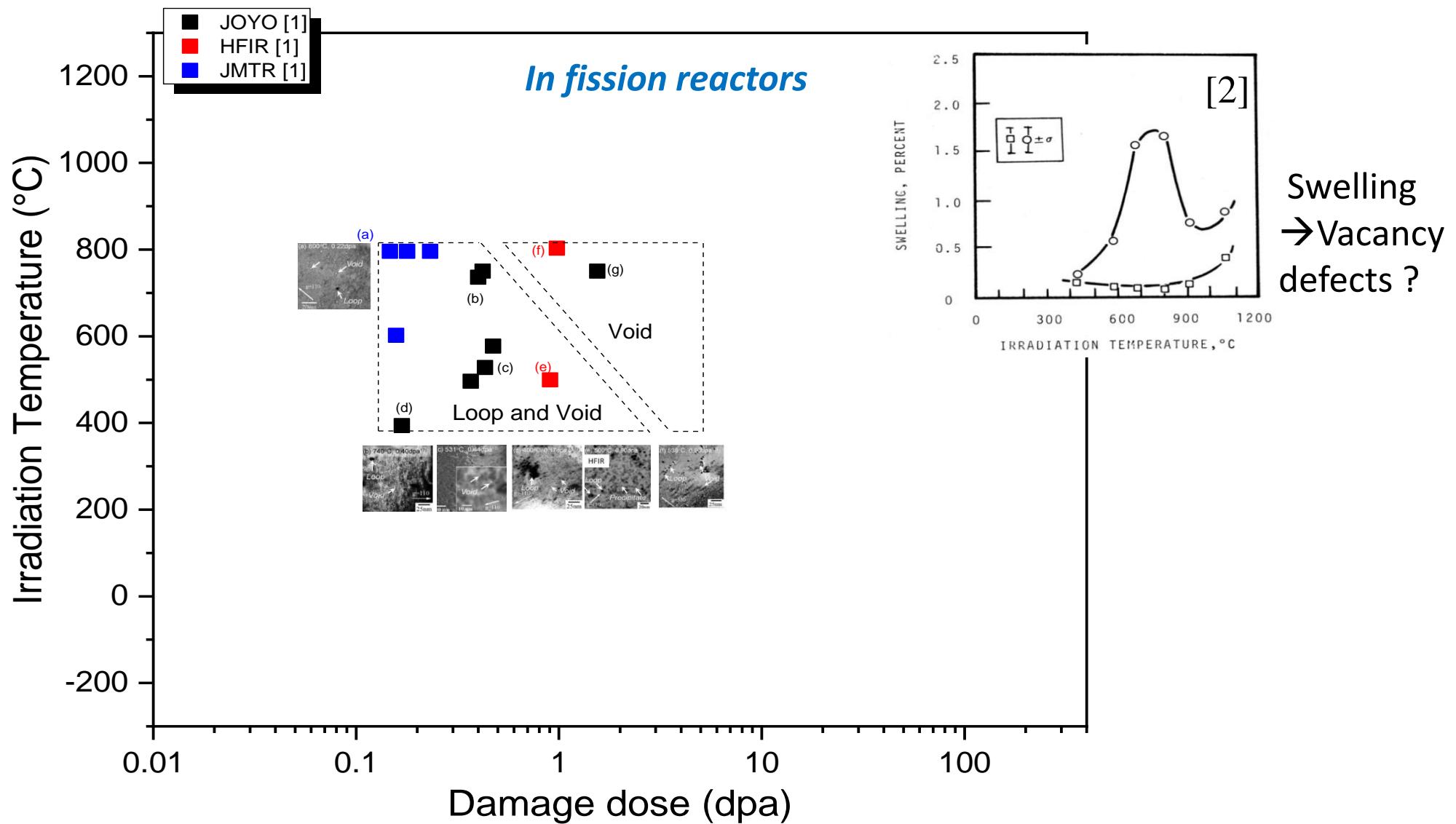
W for FW or divertor

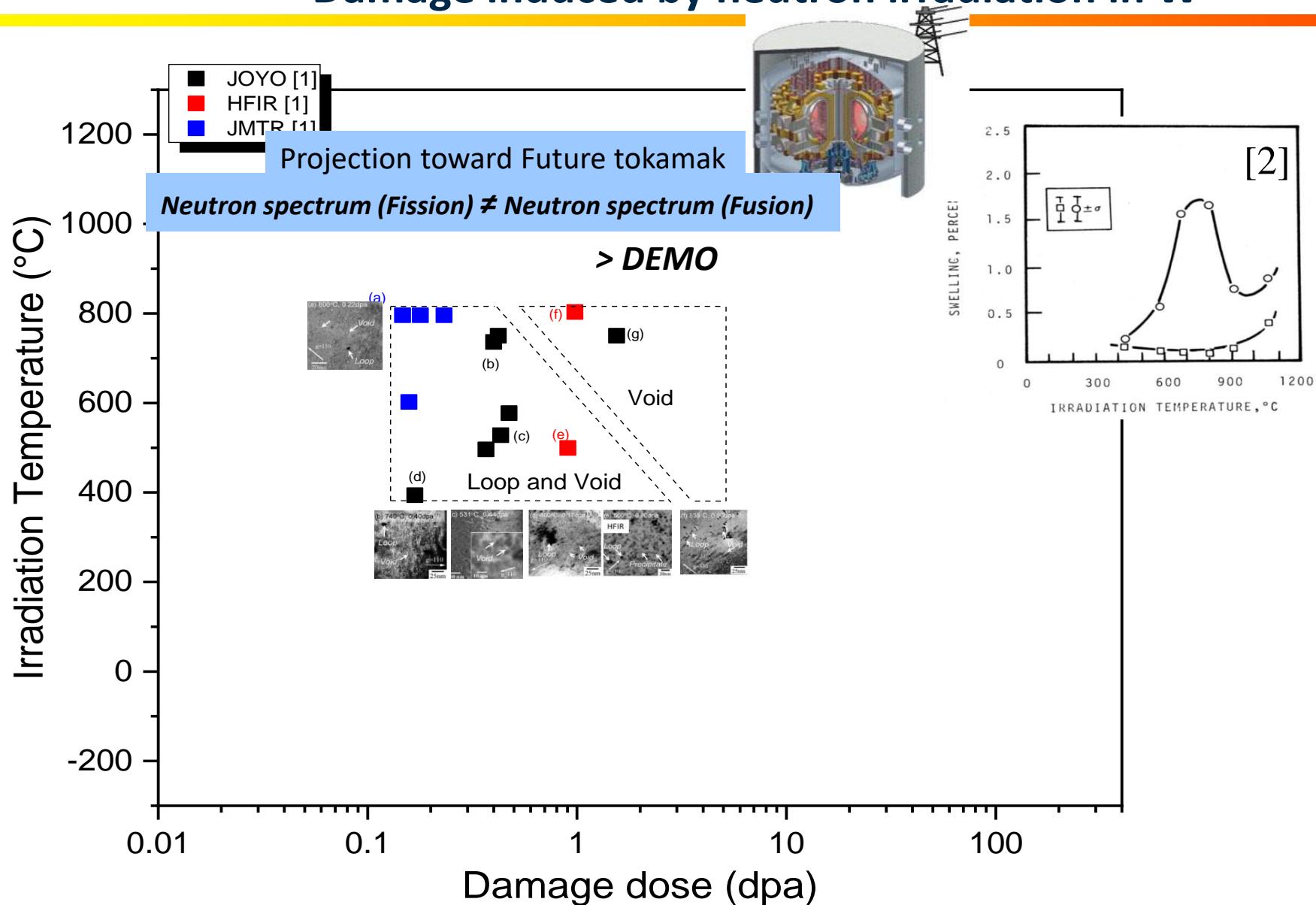
Damage dose max in 3 years = 12dpa

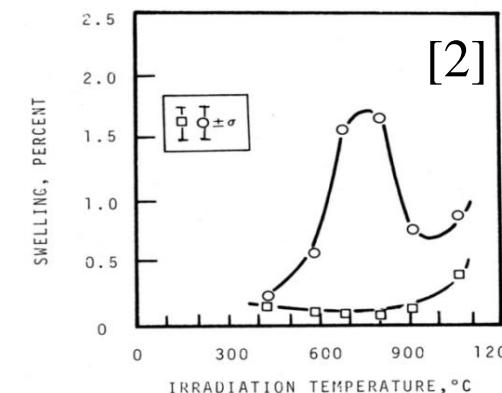
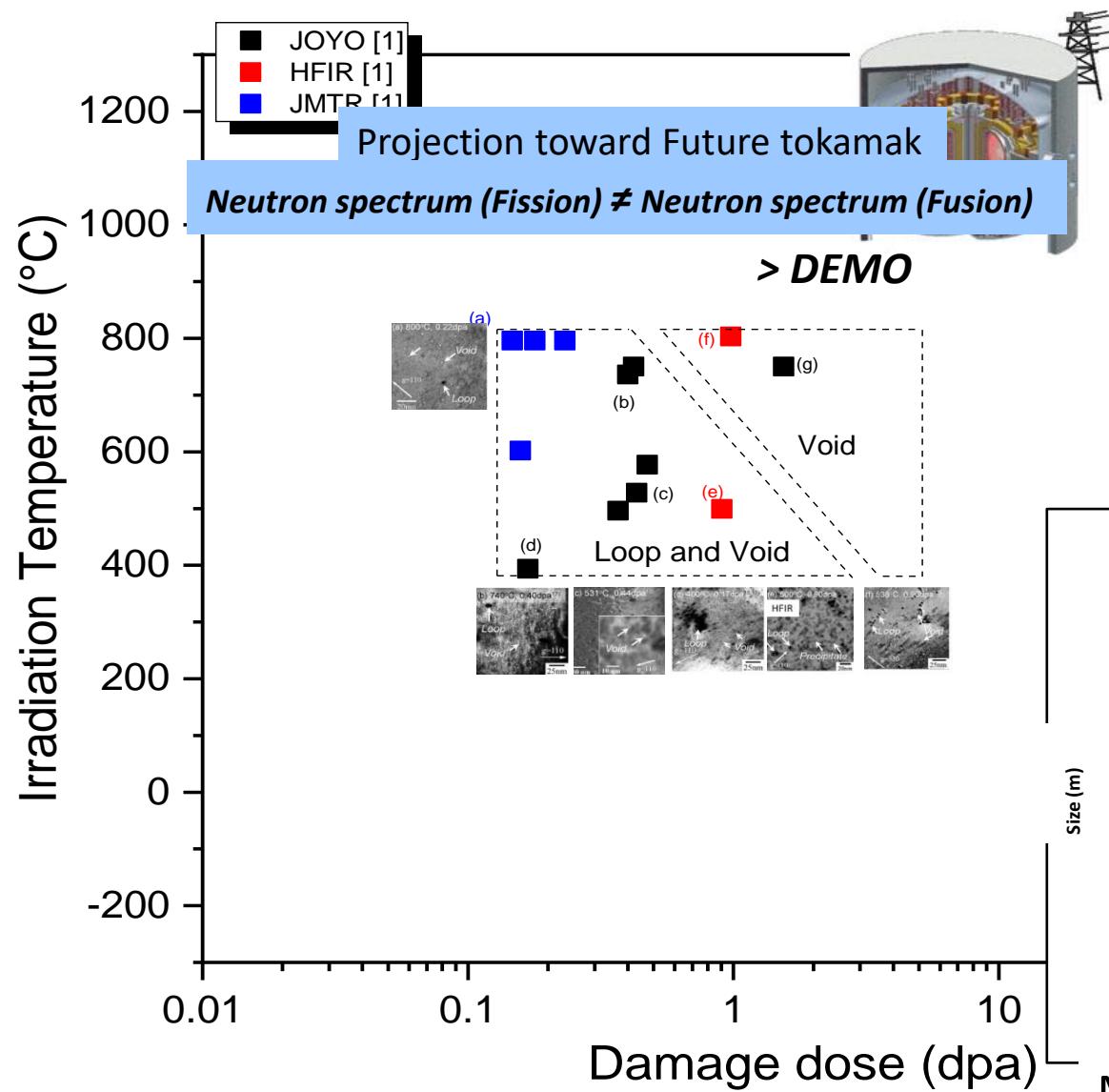


- Large energy distribution (up to 2 MeV)
mean value at 150 keV

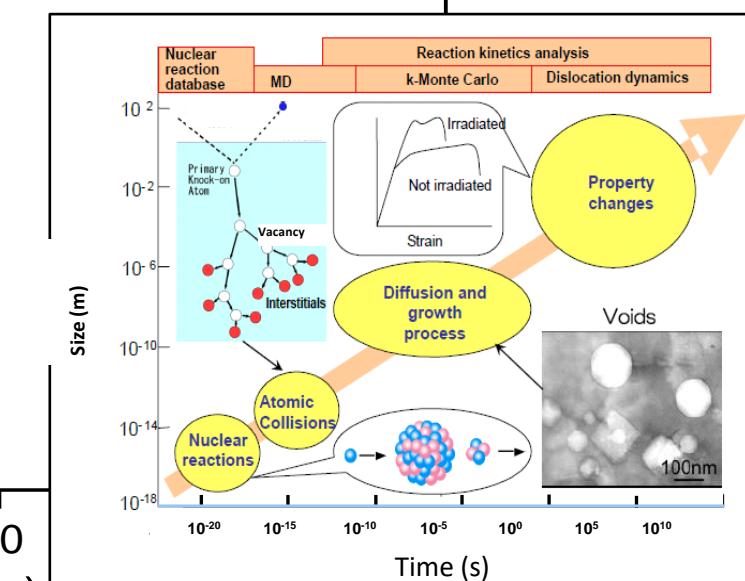






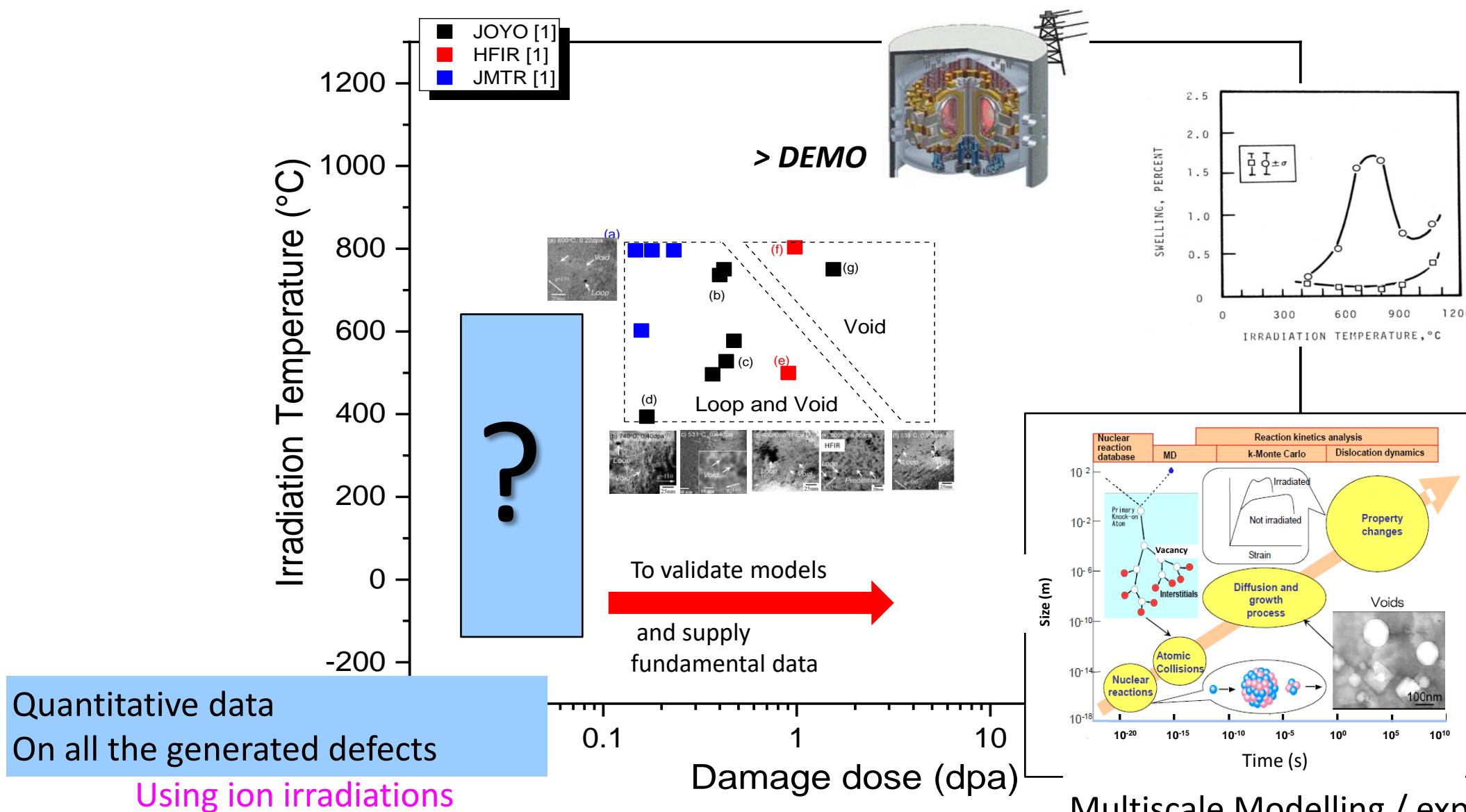


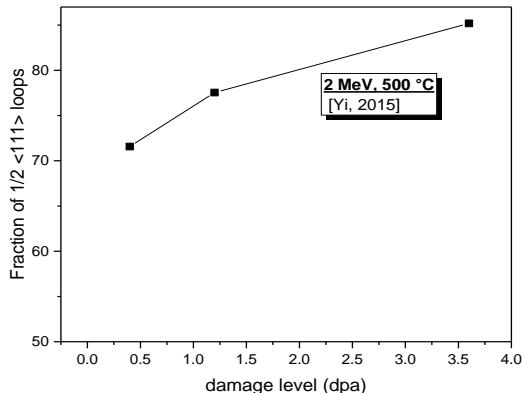
Swelling
→ Vacancy
defects ?



Multiscale Modelling / experiments

From
atomic to
macroscopic
scale



Dislocation loops: $\frac{1}{2}\langle 111 \rangle$, $\langle 100 \rangle$ 

2 MeV W, 0.4 dpa, 500°C [1] :

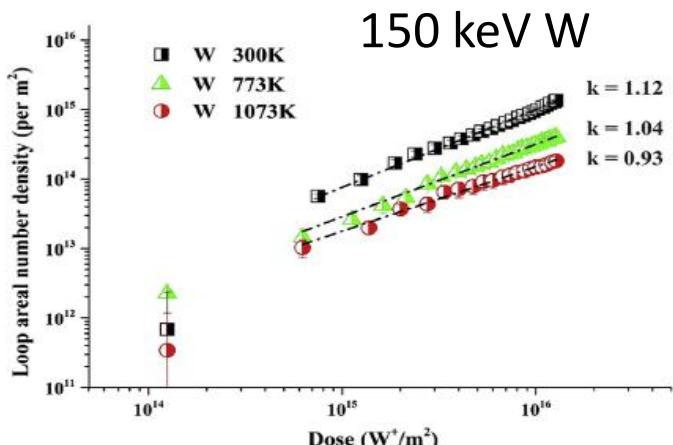
Loops $\frac{1}{2}\langle 111 \rangle$: $3.3 \times 10^{22} \text{ m}^{-3}$

mean size 3-4 nm [1]

- ✓ For irradiation at 500°C, preferential formation of $\langle 100 \rangle$ loops at low dpa

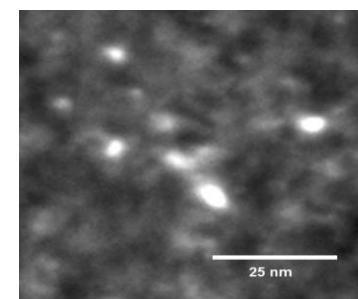
[1] X Yi et al Acta Materialia 92 (2015) 163–177

- ✓ Density and size depend on temperature

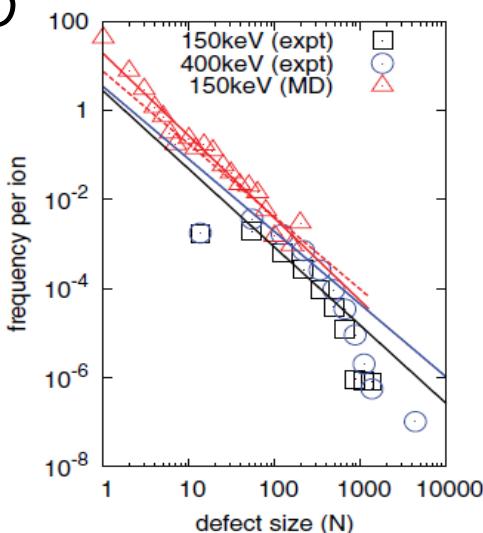


X. Yi et al. / Acta Materialia 112 (2016) 105-120

- ✓ Size distribution is a power law *as calculated in MD*



150 keV W, LN2



Yi, X., et al., EPL 110 (2015) 36001

Source of impurities

- H, He from Plasma and transmutations^[2]
bubbles, fuzz...
- Transmutation elements (Re, Os, Ta..) ^[3]
precipitates...
- Reactor's environment light elements **impurities (C, N, O...)**
- in material ^[3]

SIMS

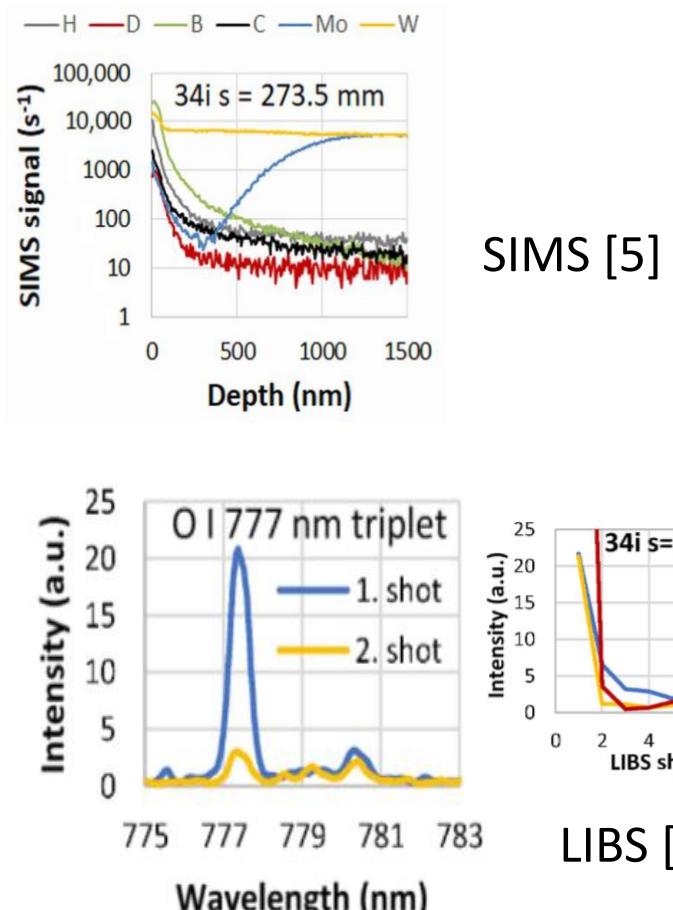
Concentration (at. ppm) (100-700 nm)		
	3N 99.95%	6N 99.9999%
H	910 ^a	Ud ^b
C	460 ^a	~ 90 ^c
N	130 ^a	Ud ^b
O	345 ^a	~ < 65 ^c ~ 100 ^c

a/ provided concentration by supplier b/ undetectable by LA-ICP-MS c/ SIMS

- plasma (C, N, O... in WEST⁵)

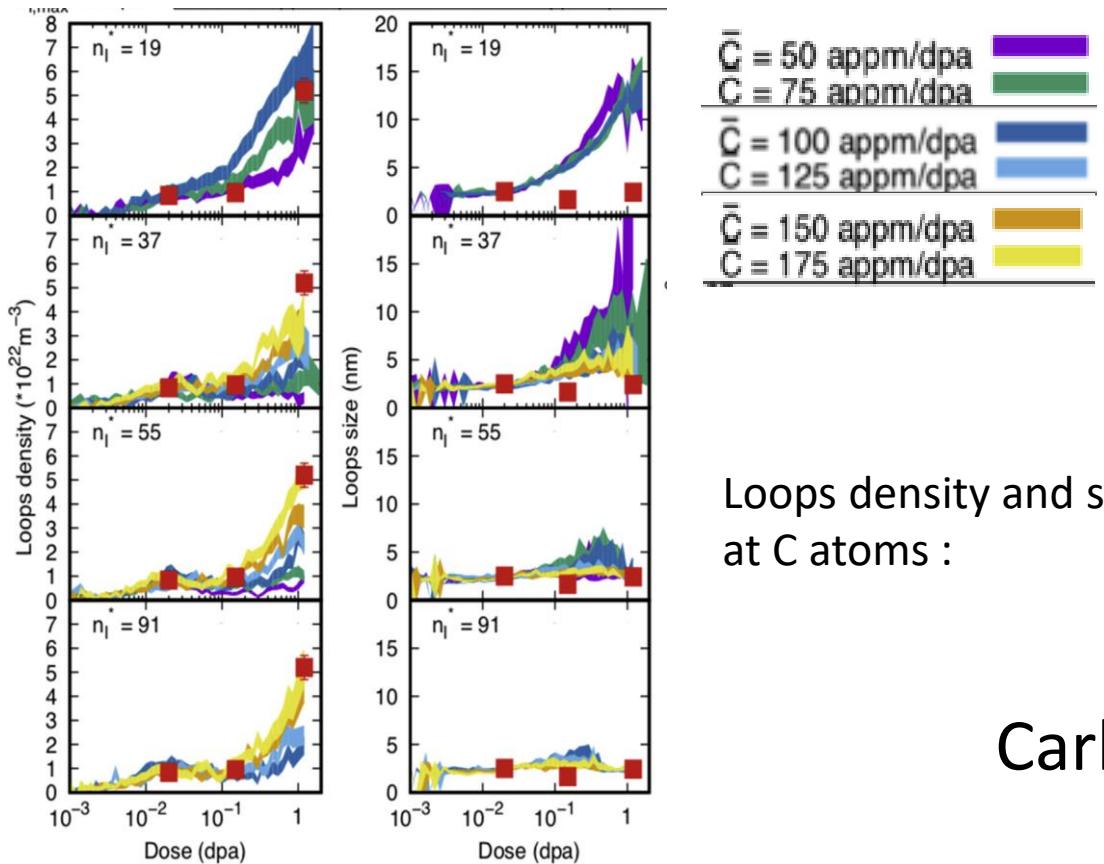
- Impurity in plasma
- Impurity-defects complexes and role on microstructure

WEST Campaign C3 [5]





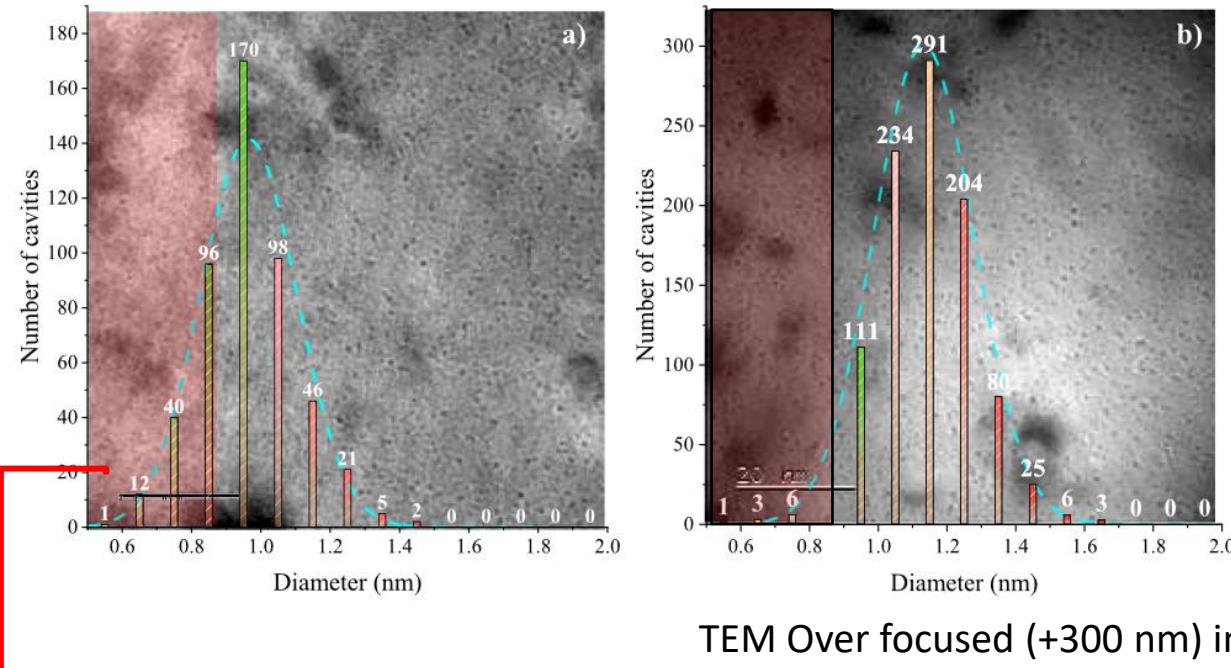
Impurity-defects complexes Carbon in tungsten



OKMC (Object Kinetic Monte Carlo) simulations [6]

Loops density and size depends on C content due to trapping of loops at C atoms :

Carbon can trap dislocation loops



1.2 MeV W, 0.02 dpa, 500°C in 3N and 6N W [1] :

Damage level (dpa)	0.02	
Observation conditions	JEOL ARM200, 200 kV, 500 kX,	
Irradiation Temperature (°C)		500
Purity	3N-HP	6N-XHP
Thickness (nm)	55 ± 20 (EFTEM)	90 ± 30 (EFTEM)
Mean diameter (nm)	0.97 ± 0.19	1.13 ± 0.21
Density (10^{24} m^{-3})	1.73 ± 0.71	1.56 ± 0.52
Swelling%	0.09 ± 0.02	0.12 ± 0.04

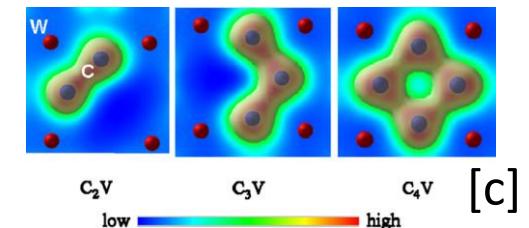
Small vacancy defects (<1nm) ? By TEM difficult to observe and to count them

Less data on vacancy defects and cavities

→ Self irradiations and characterization of the microstructure using TEM and PAS

Impurity-Vacancy interactions

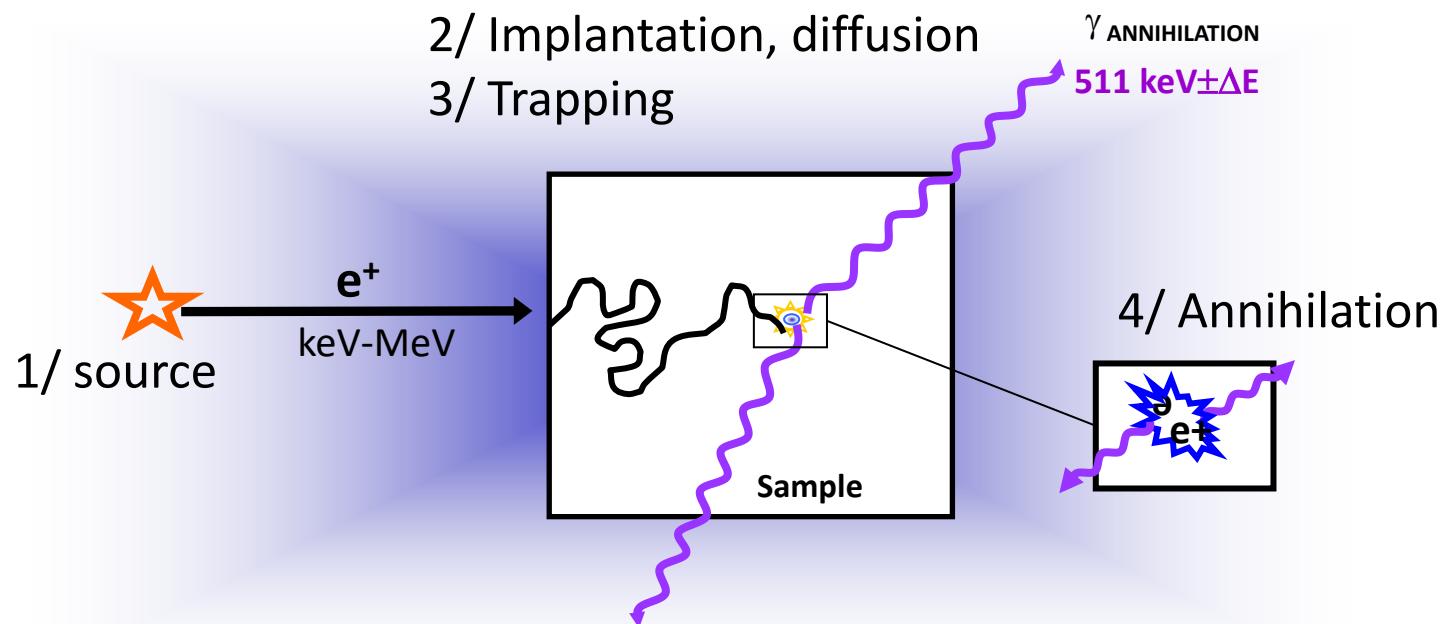
DFT calculations	X	E_m^X (eV)	$E_b^{V-X_1}$ (eV)	$E_{diss}^{V-X_1}$ (eV)
	H	0.21 (TIS-TIS) [24]	1.24 [a]	1.45
	C	1.46 (TIS-OIS) [20]	1.93 [b]	3.39
	N	0.73 (TIS-OIS) [26]	2.48 [c]	3.21
	O	0.17 (TIS-TIS) [22]	3.05 [d]	3.22



Strong interaction between **Vacancy** interactions with **LEs** (H,C,N,O..)

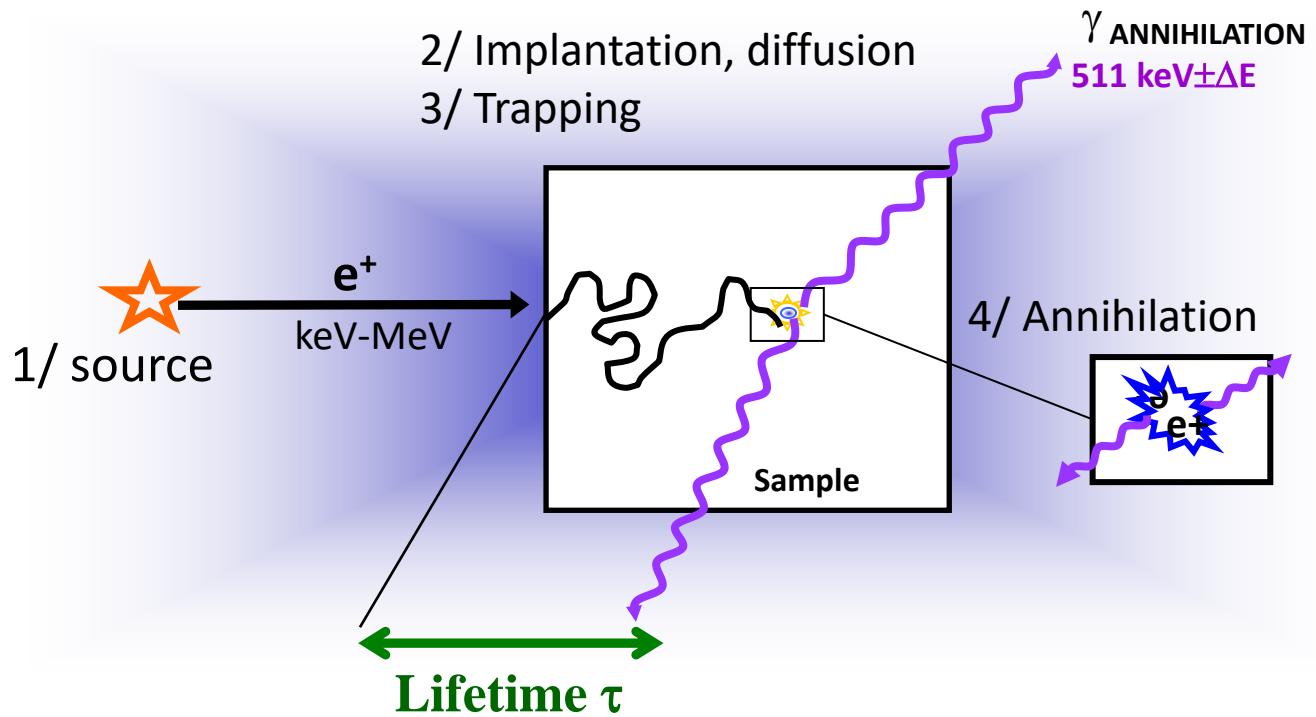
Positron Annihilation Spectroscopy is based on 2 properties of positron

- ✓ As antiparticle of electron, positron annihilates with it, leading to emission of **2 γ rays** : $E = 511 \text{ keV} \pm \Delta E$
- ✓ **Trapping** in vacancy defects



→ Electronic Structure of solids

Probe for **vacancy defects and free volumes**



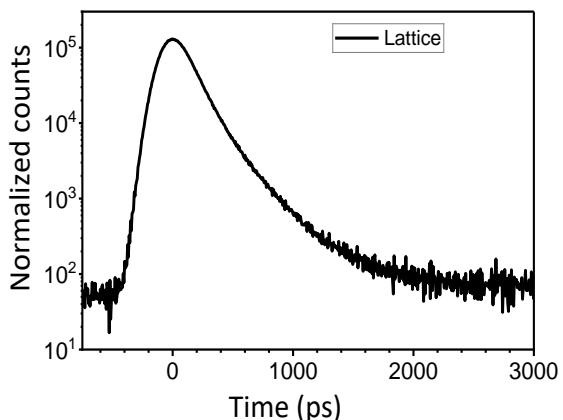
$$\tau = (\pi r_0^2 c n_{e^-}^*)^{-1}$$

r_0 : electron radius

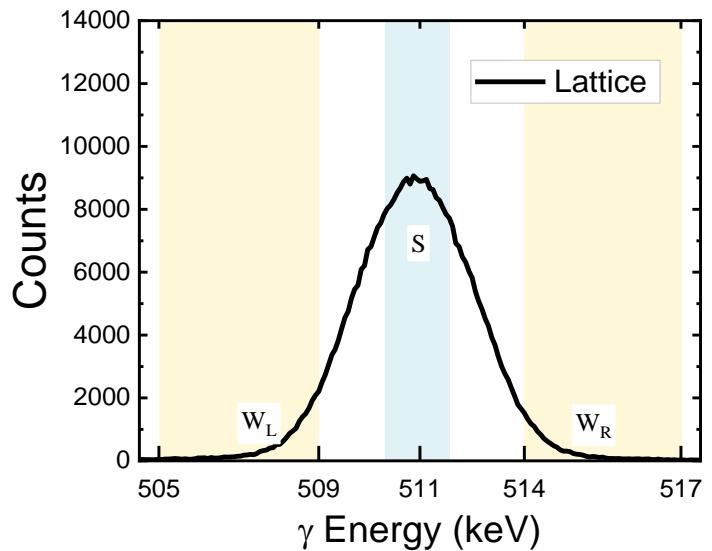
c : light velocity

$n_{e^-}^*$: local electronic density

PALS



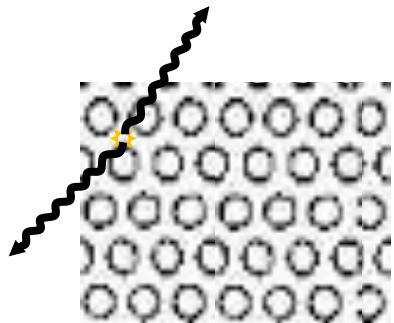
Doppler broadening Spectroscopy



Annihilation fractions of $e^- e^+$

S = with low momentum

W = with high momentum


 τ_L, S_L, W_L

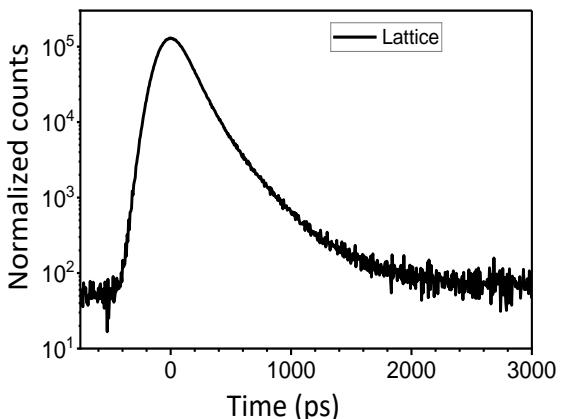
Annihilation characteristics in perfect **Lattice**
(without defects)

$$\tau = (\pi r_0^2 c n_{e^-}^*)^{-1}$$

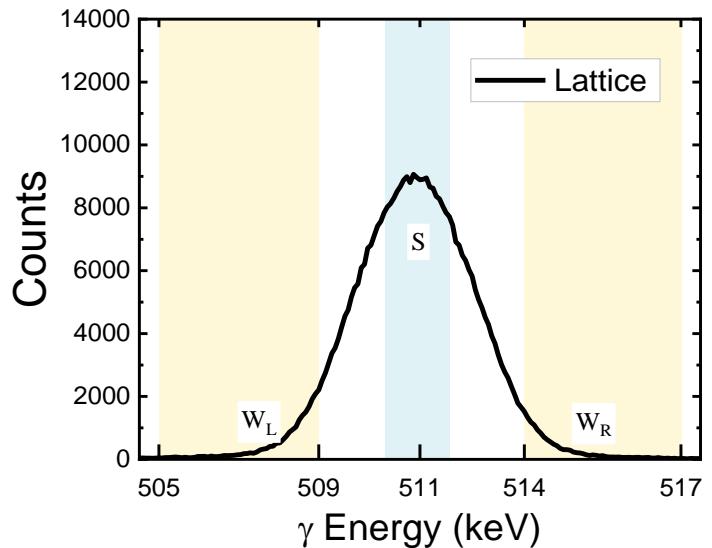
r_0 : electron radius

c : light velocity

$n_{e^-}^*$: local electronic density

PALS


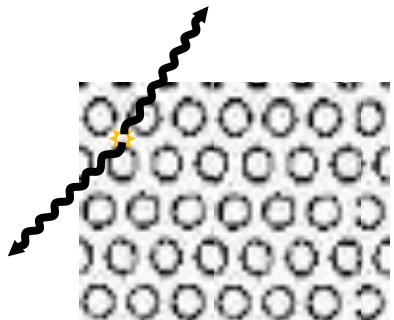
Doppler broadening Spectroscopy



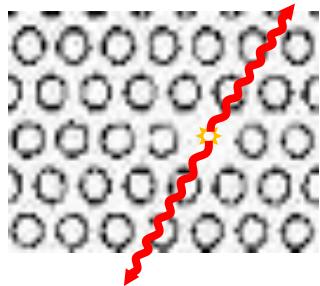
Annihilation fractions of e- e+

S = with low momentum

W = with high momentum


 τ_L, S_L, W_L

Annihilation characteristics in perfect **Lattice**
(without defects)


 τ_V, S_V, W_V

Annihilation characteristics of **Vacancy**

$$\tau = (\pi r_0^2 c n_{e-}^*)^{-1}$$

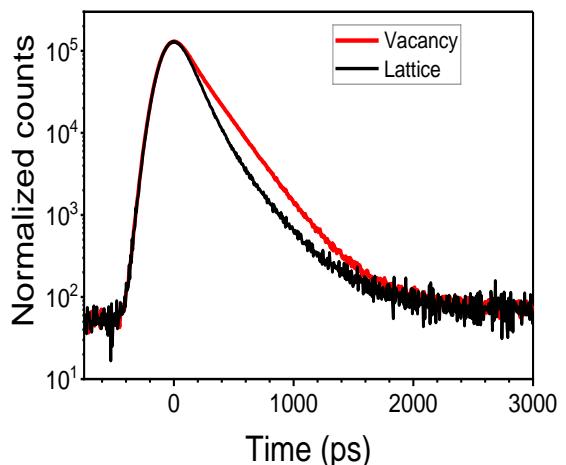
r_0 : electron radius

c : light velocity

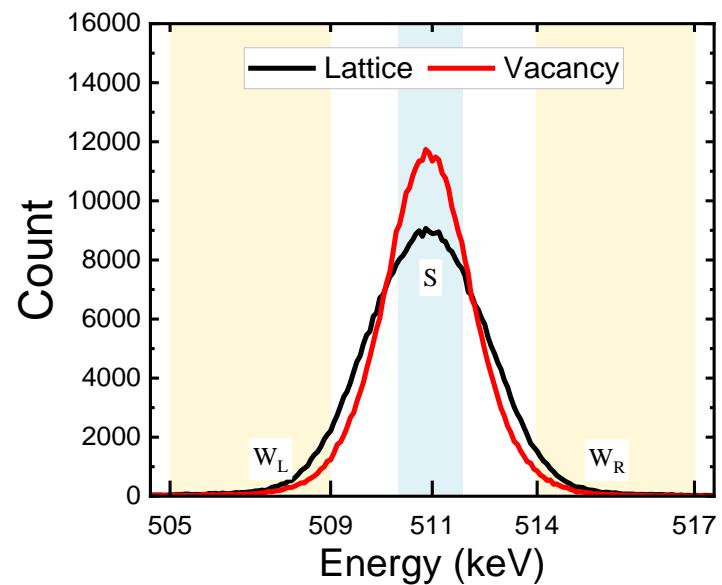
n_{e-}^* : local electronic density

Lifetime t

PALS



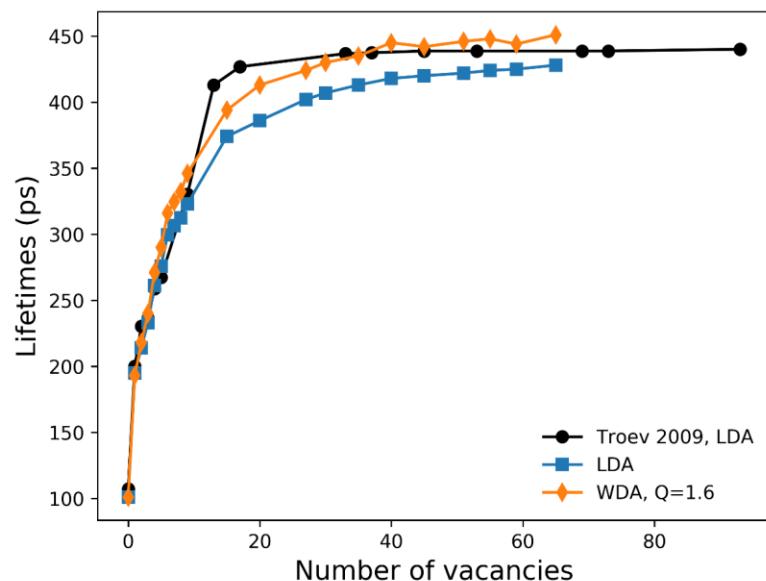
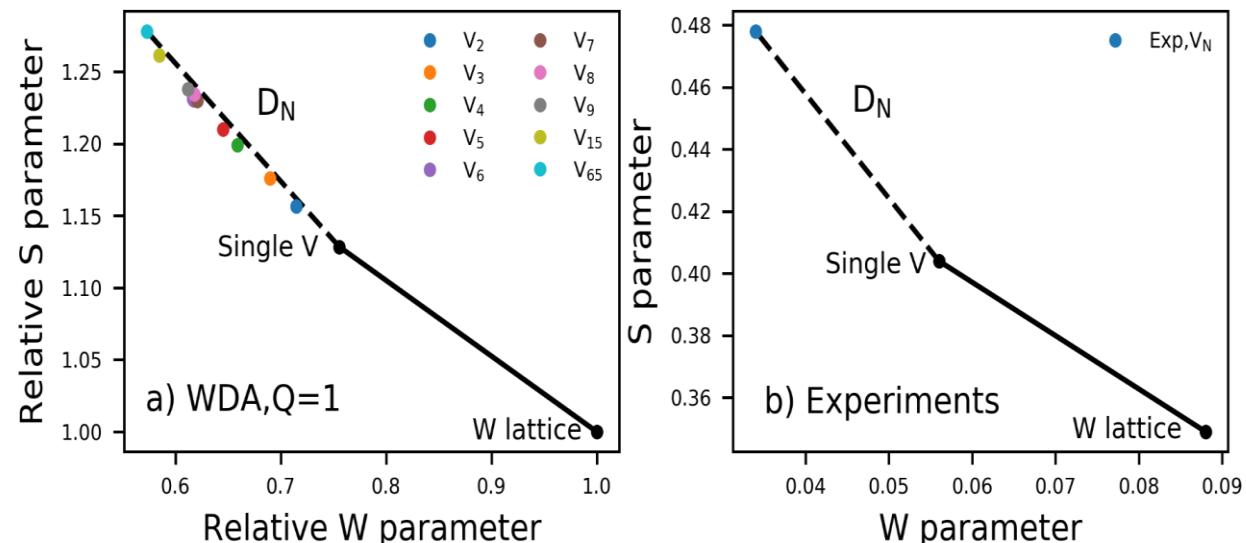
Doppler broadening Spectroscopy



Vacancy defects

τ, S increases

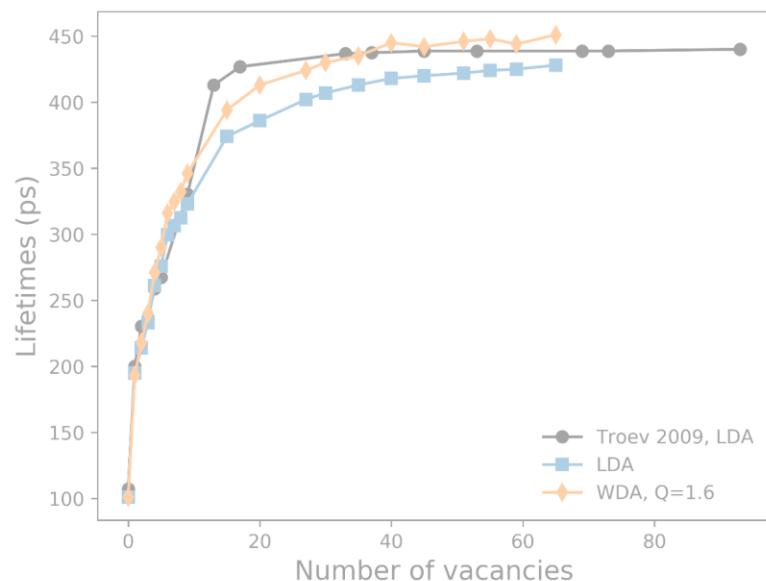
W decreases

Lifetime τ **Doppler broadening Spectroscopy (S & W)**

Exp: $\tau_L = 105 \pm 3$ ps
 $\tau_V = 200 \pm 5$ ps

N in V_N increases
 τ_{VN} , S_{VN} increases
 W_{VN} decreases
Until saturation for $N \sim 30$

*In vacancy clusters : WDA (Q=1)

Lifetime τ Exp: $\tau_L = 105 \pm 3$ ps $\tau_V = 200 \pm 5$ ps

Oigui Yang^a, Zhiwei Hu^b, Iija Makkonen^c, Pierre Desgardin^b, Werner Egger^d,
Murielle-France Barthe^{b,c}, Par Olsson^{a,d}

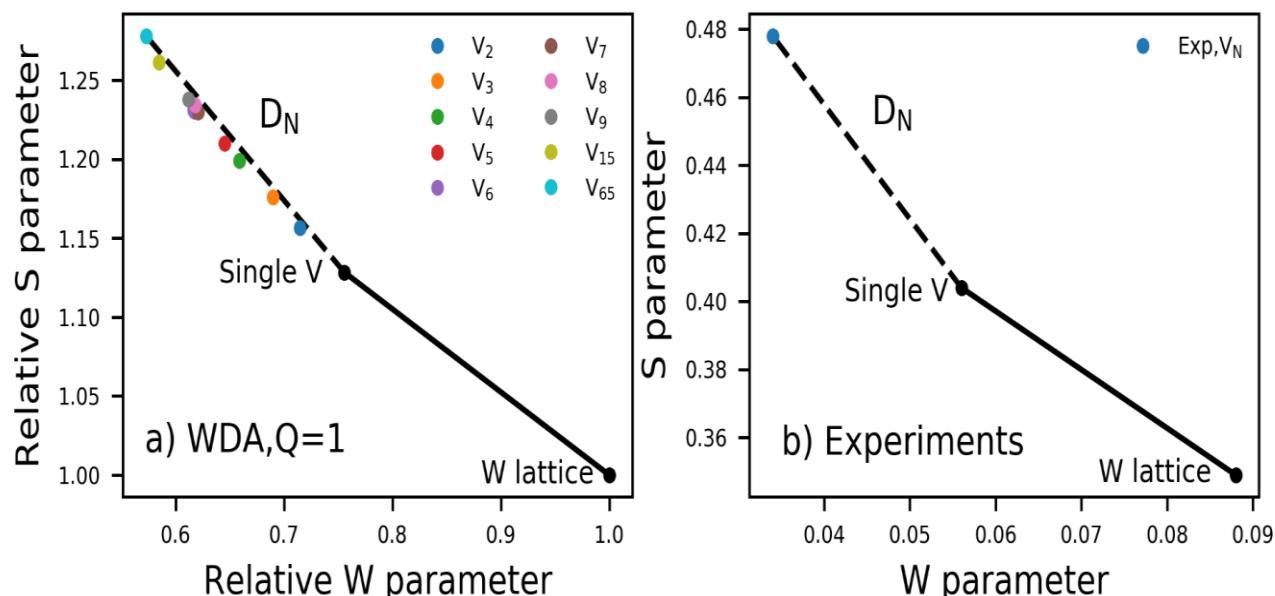
^aKTH Royal Institute of Technology, Nuclear Engineering, Roslagstullsbacken 21, 114 21 Stockholm, Sweden

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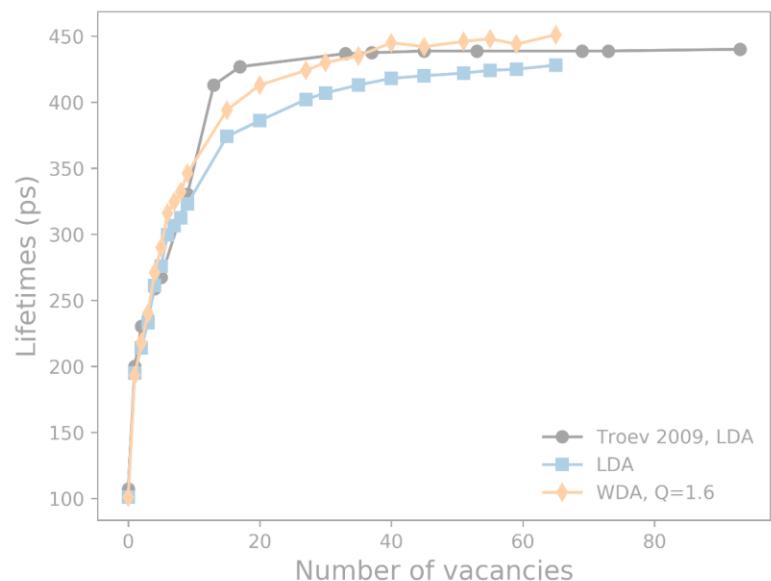
Doppler broadening Spectroscopy (S & W)



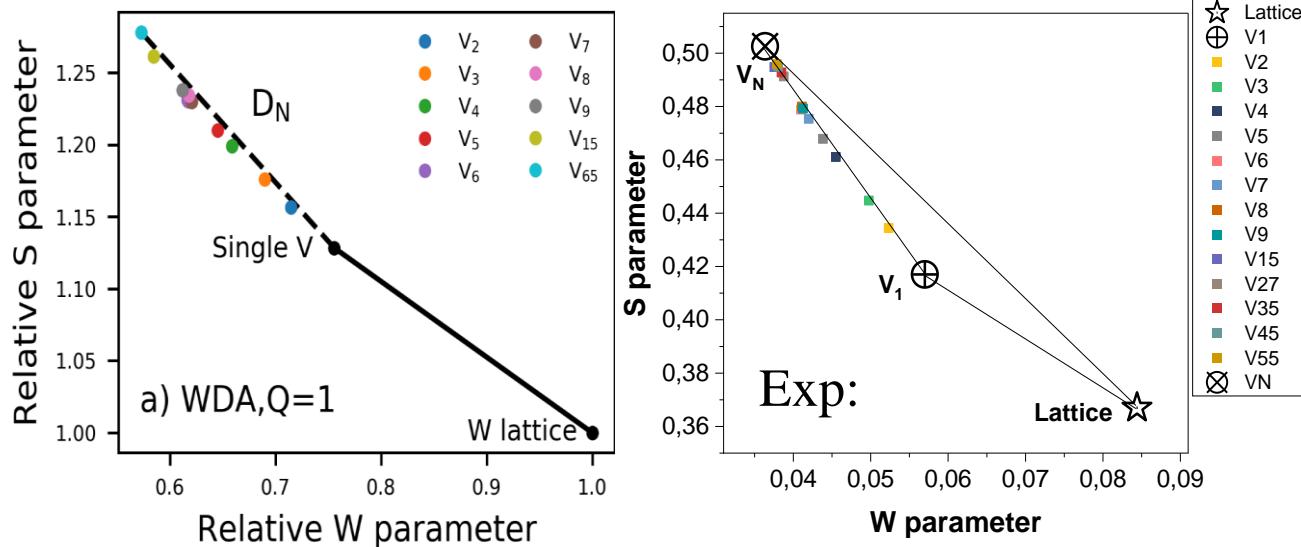
*In vacancy clusters : WDA (Q=1)

SW points aligned on a straight line D_N
Same trend for both experiment and theory



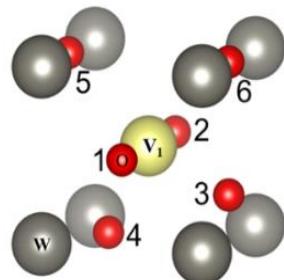
Lifetime τ Exp: $\tau_L = 105 \pm 3$ ps $\tau_V = 200 \pm 5$ ps

Doppler broadening Spectroscopy (S & W)



Relative S & W annihilation characteristics

- One V_1 can trap until 6 O atoms, forming $O_{1-6}V_1$ complexes [1]



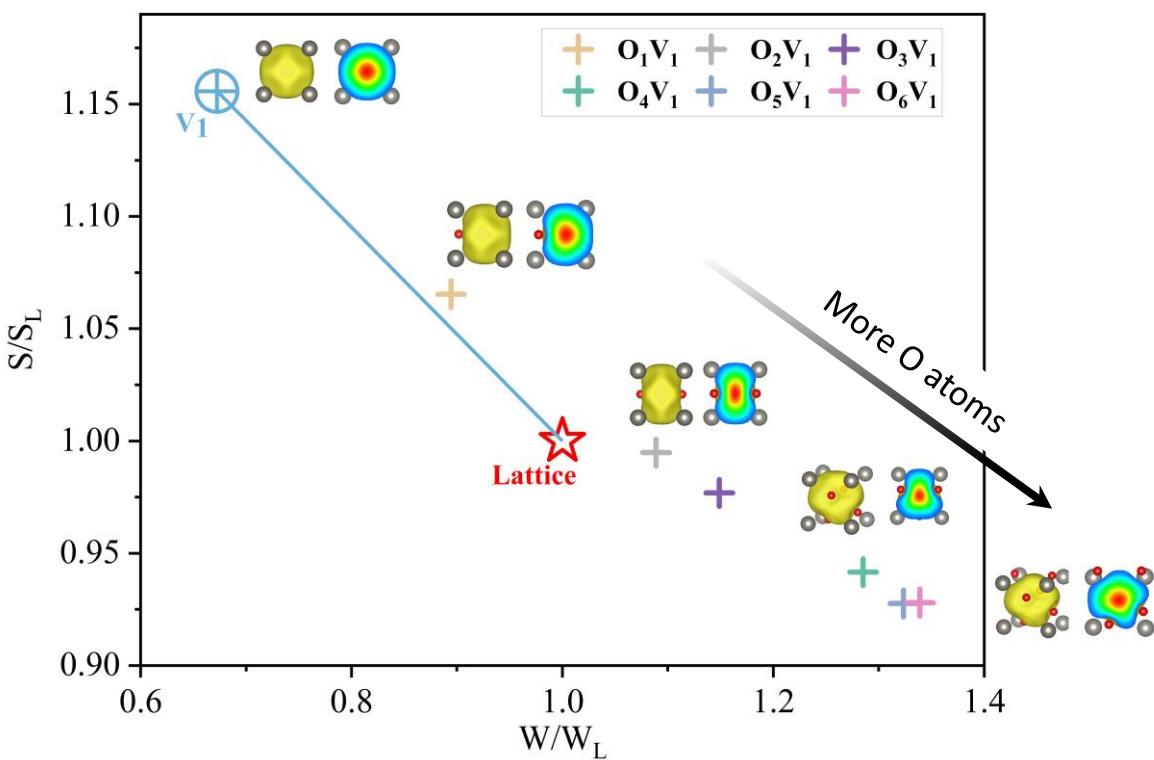
PALS [3]

O_pV_1 , p	$E_{binding}^{O_pV_1}$ (eV)	τ (ps)
1	3.0	170
2	5.9	142
3	6.9	143
4	8.56	130
5	10.06	124
6	11.92	132

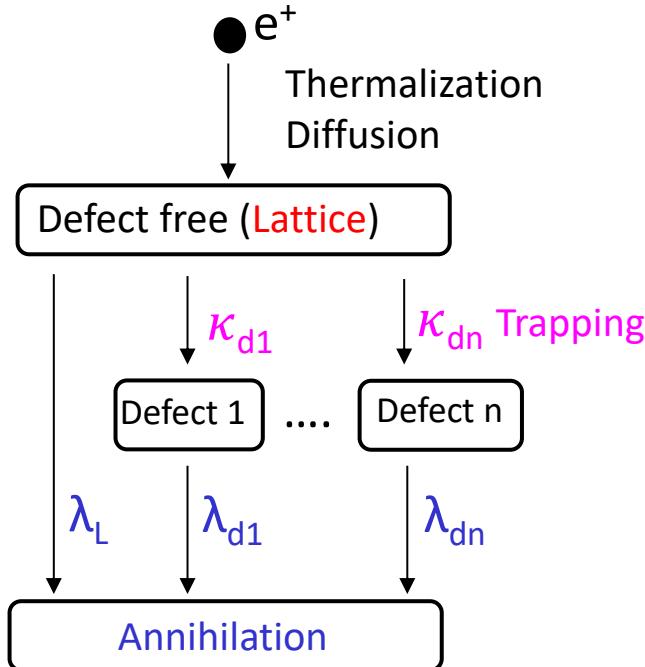
More O atoms

Pure V_1 , $\tau_{V_1}=195$ ps (Theo.) [2]

DB-PAS [3]



Assuming **n independent defects and no de-trapping from defects [1]**



$$1. PALS(t) = R(t) * \sum \left(\frac{I_{di}}{\tau_{di}} e^{-\frac{t}{\tau_i}} \right) + \frac{I_1}{\tau_1} e^{-\frac{t}{\tau_1}} + BG \quad R(t), BG: \text{experimental values}$$

$$2. \begin{cases} S = S_L \cdot f_L + \sum S_{di} \cdot f_{di} \\ W = W_L \cdot f_L + \sum W_{di} \cdot f_{di} \end{cases} \quad \tau_{di}, S_{di} \text{ and } W_{di} \text{ calculated using TCDFT}$$

$$\begin{cases} I_{di} = \frac{k_{di}}{\lambda_L - \lambda_i + \sum k_{di}}, \text{ and } I_1 + \sum_{di} I_{di} = 1 & I_i: \text{Intensity of lifetime component i} \\ f_{di} = \frac{k_{di}}{\lambda_L + \sum k_{di}}, \text{ and } f_L + \sum_{di} f_{di} = 1 & f_i: \text{Fraction of annihilation state i} \end{cases}$$

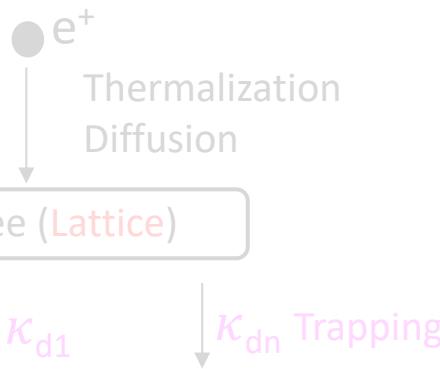
Where trapping rate, $K_{di} = c_{di} \cdot \mu_{di}$

c_{di} : vacancy (V_i) concentration

μ_{di} : specific trapping coefficient

Assuming n independent defects and no de-trapping from defects [1]

Theoretical S , W , and PALS(t)



1. $PALS(t) = R(t) * \sum \left(\frac{I_i}{\tau_i} e^{-\frac{t}{\tau_i}} + \frac{I_1}{\tau_1} e^{-\frac{t}{\tau_1}} \right) + BG$
 $R(t)$, BG : experimental values
2. $\begin{cases} S = S_L \cdot f_L + \sum S_i \cdot f_i \\ W = W_L \cdot f_L + \sum W_i \cdot f_i \end{cases}$
 τ_i , S_i and W_i calculated using TCDFT

- Vacancy distribution (C_i) can be extracted from Experimental data : PALS spectrum, S_{exp} , W_{exp}
- Or
- PALS spectrum, S , W can be calculated and compared to Experimental data

Annihilation

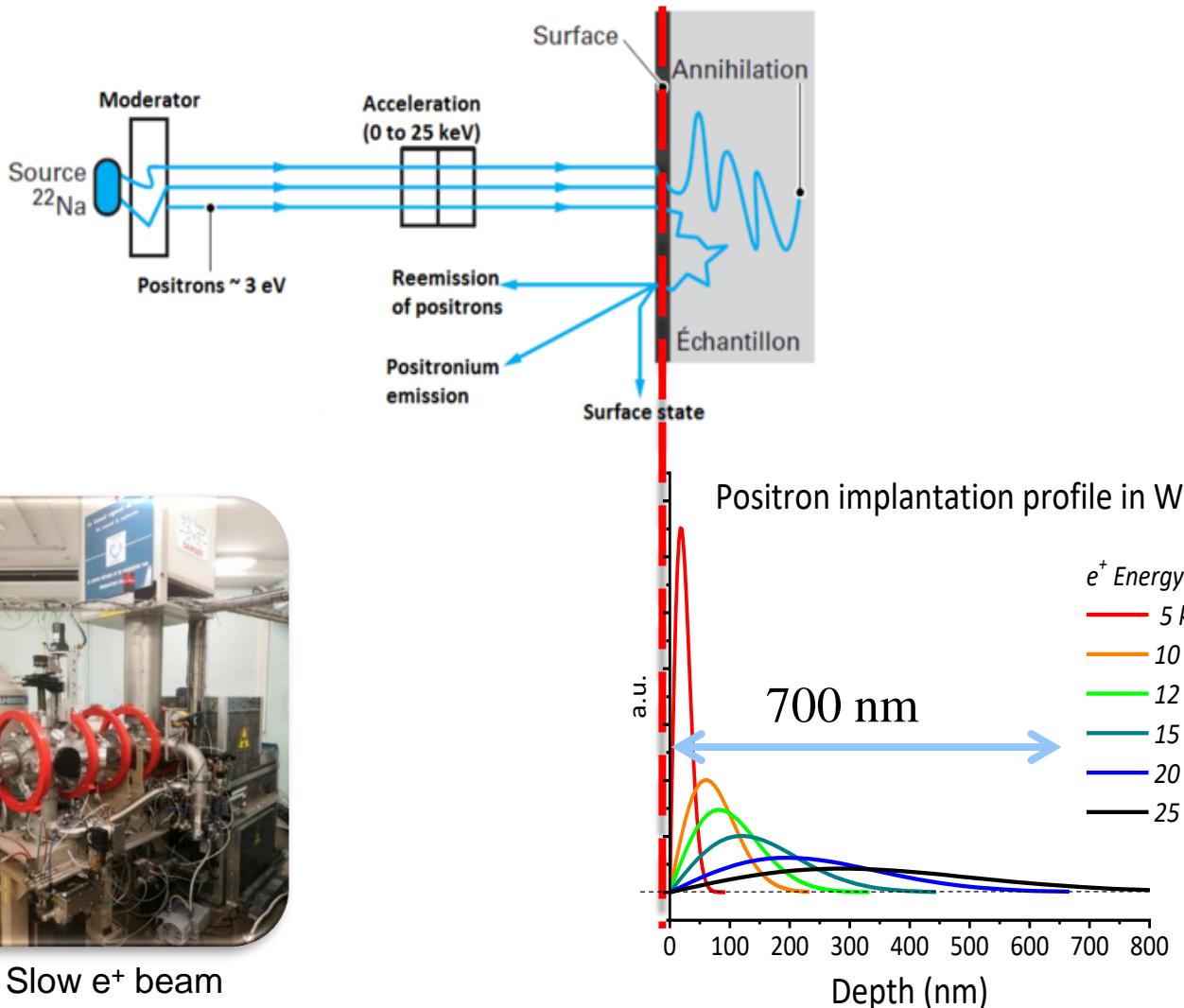
Where trapping rate, $\kappa_i = c_i \cdot \mu_i$

c_i : vacancy (V_i) concentration

μ_i : specific trapping coefficient



Slow e^+ beam
at CEMHTI



Variable slow positron beam + Doppler Broadening

Monoenergetic e^+ beam ($\varnothing 2\text{-}3\text{mm}$, $10^5 \text{ e}^+\cdot\text{cm}^{-2}\cdot\text{s}^{-1}$) from 0.5 to 25 keV [1]

→ $S(E)$ and $W(E)$
Vacancy-type defects in
thin layers

✓ 2 illustrations

- Oxygen vacancy interactions
- Vacancy clusters distribution in self-irradiated tungsten

✓ 2 illustrations

- Oxygen vacancy interactions
- Vacancy clusters distribution in self-irradiated tungsten

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Revealing the role of oxygen on the defect evolution of electron-irradiated tungsten: A combined experimental and simulation study

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Jérôme Joseph^a, Pär Olsson^b, Thomas Jourdan^d, Marie-France Barthe^{a,*}

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^b KTH Royal Institute of Technology, Nuclear Engineering, Roslagstullsbacken 21, 114 21 Stockholm, Sweden

^c Groupe d'Etude de la Matière Condensée, CNRS, UVSQ, 45 avenue des Etats-Unis, 78035 Versailles Cedex, France

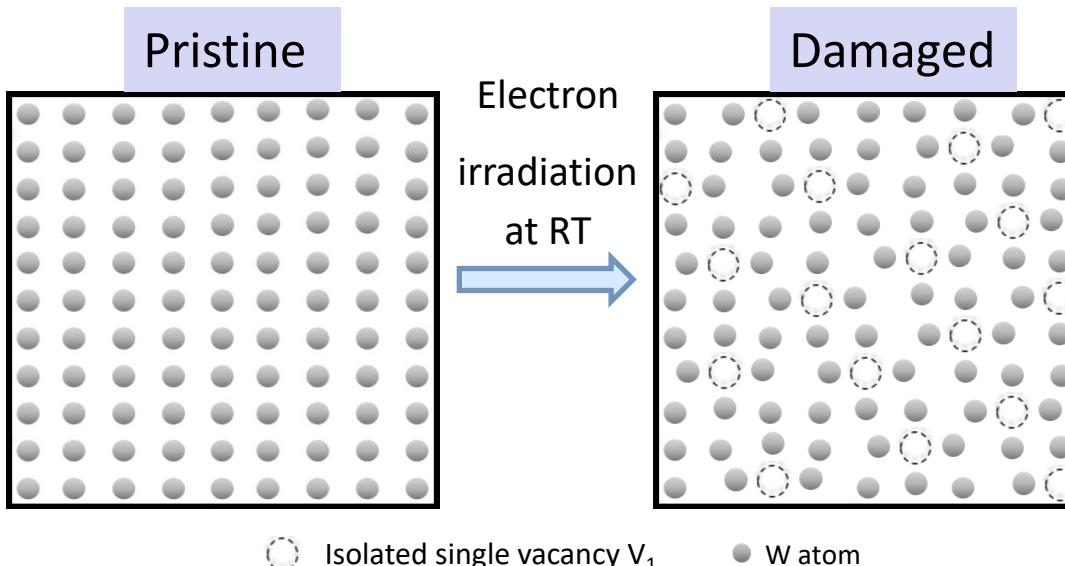
^d Université Paris-Saclay, CEA, Service de recherche en Corrosion et Comportement des Matériaux, SRMP, F-91191 Gif-sur-Yvette, France

^e Institute of High Energy Physics, CAS, 100049 Beijing, China

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2.5 MeV electron irradiation at Room temperature (RT)

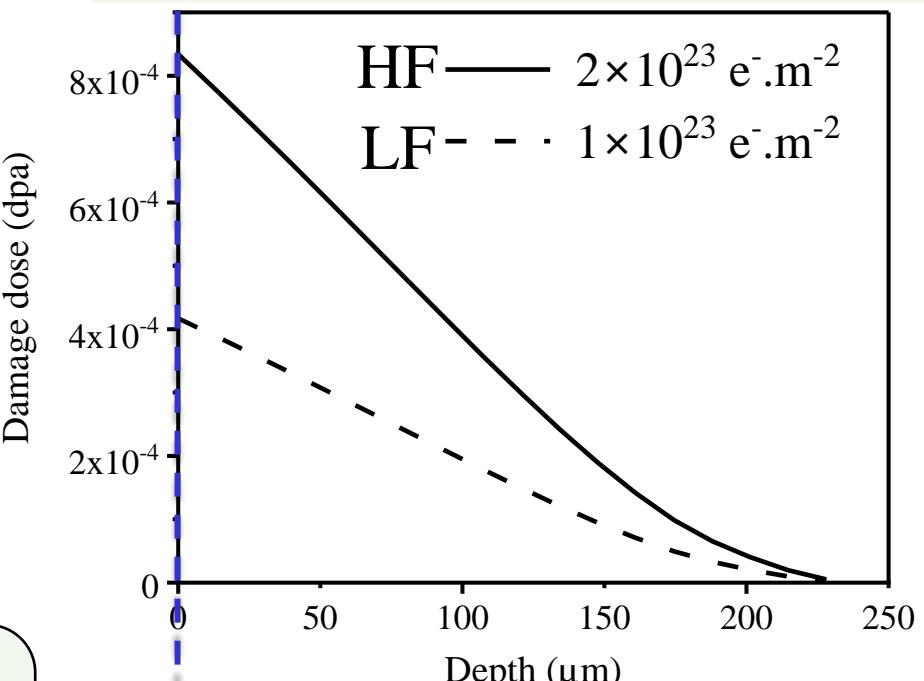
99,95% (3N) polycrystalline tungsten



Characterizations

- Positron annihilation spectroscopy (PAS) : Vacancy-type defects
- SIMS : LE atom Impurities

Damage profiles using POLY et SMOTT code [1-3]



Max damage

HF: $\sim 8 \times 10^{-4}$ dpa

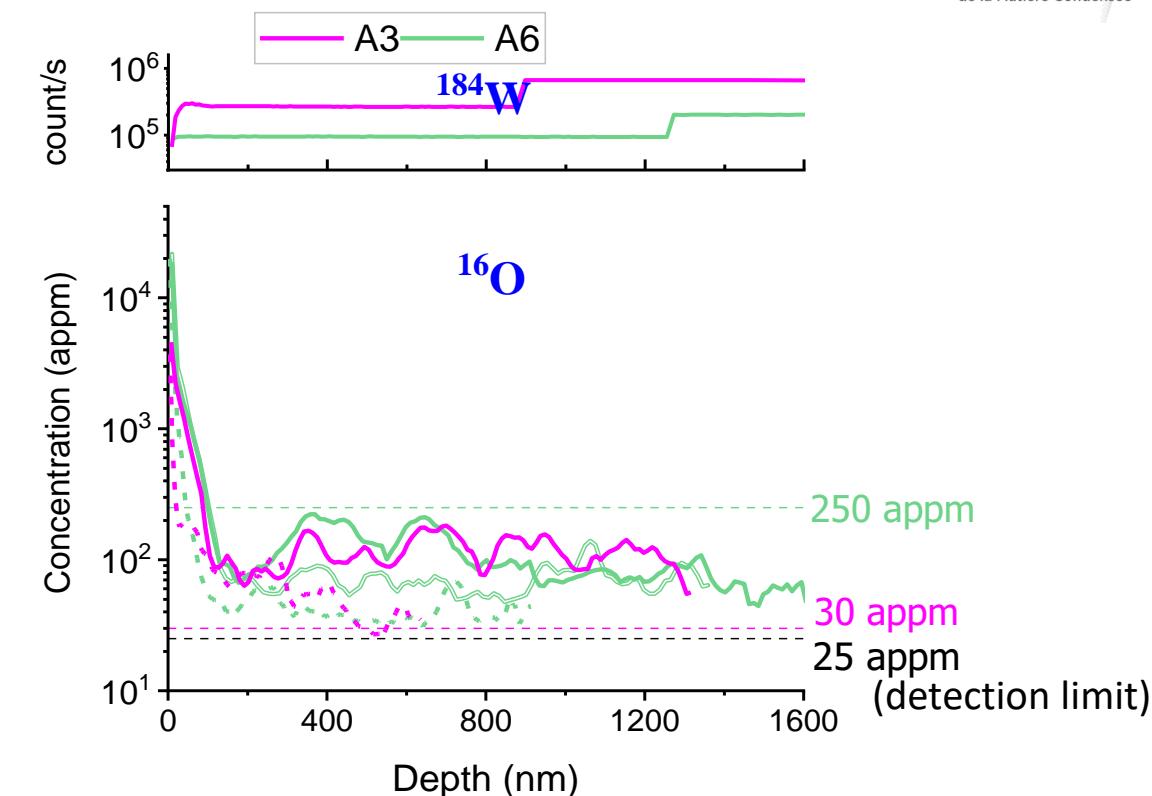
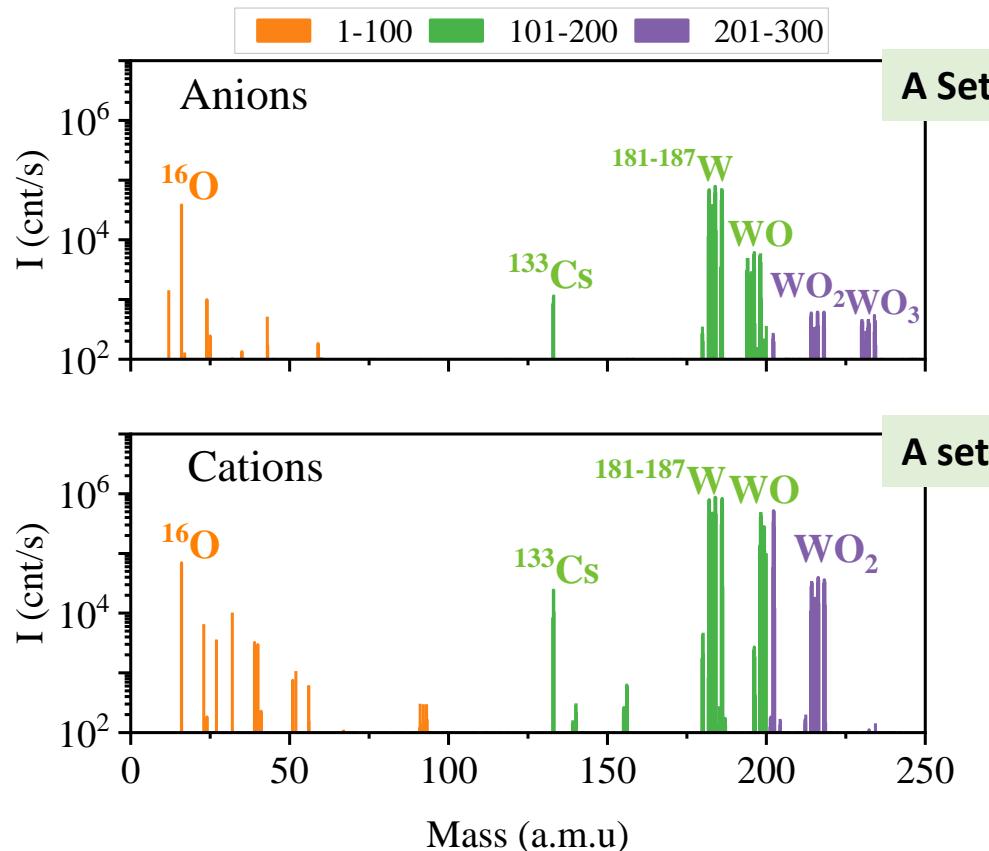
LF: $\sim 4 \times 10^{-4}$ dpa

[1] McKinley et Feshbach, PHYS. REV. 74 (1948) 1759–1763

[2] Lesueur, PMA 44 (1981) 905–929

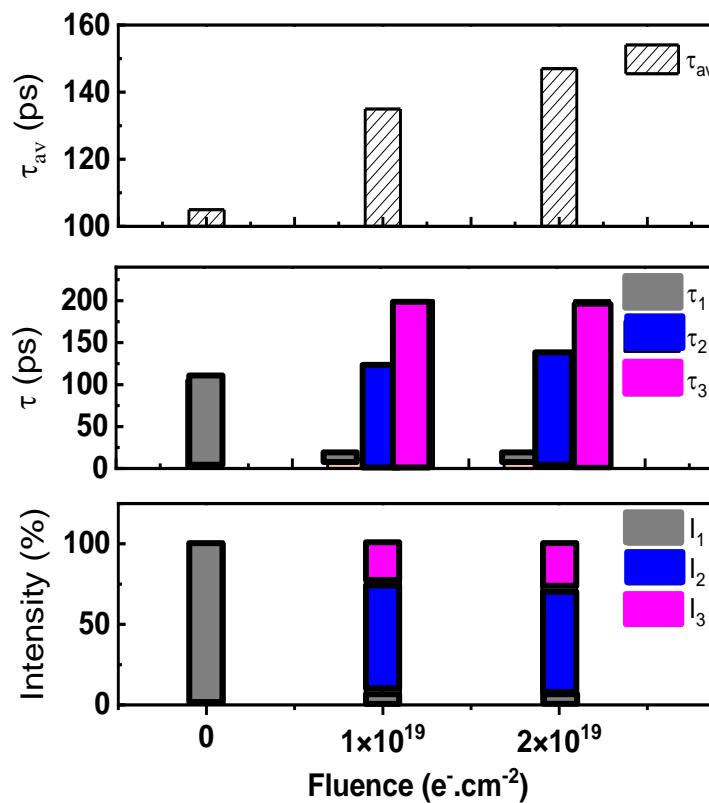
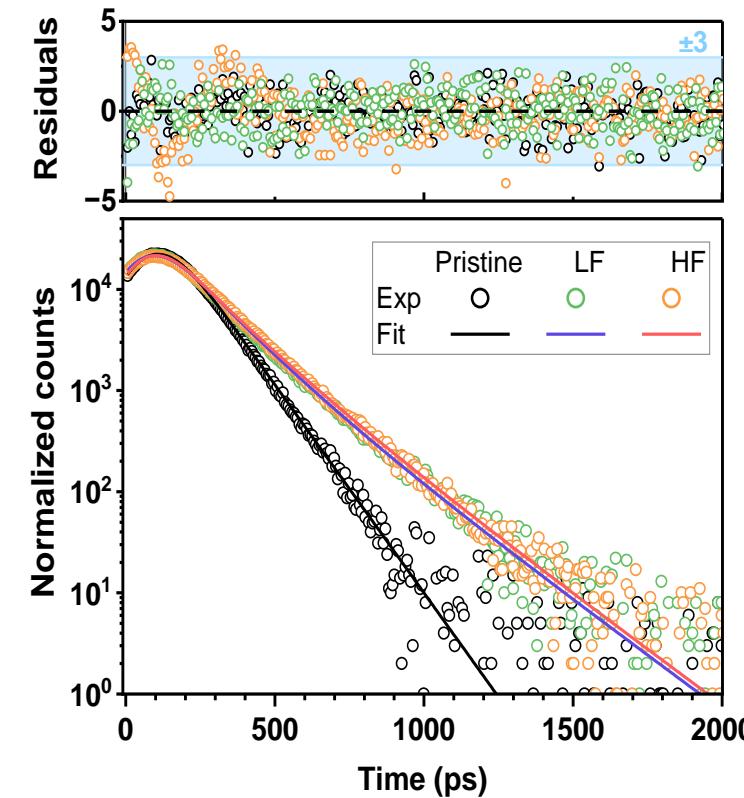
[3] Dunlop et al. NIMPRSB 42 (1989) 182–192

O Quantification in irradiated samples A3, and in the pristine sample A6



- Significant signal of Oxygen (O) and oxygen-tungsten molecules (WO_{1-3})

- A set: heterogeneous distribution,
[O]: 30-250 appm.



3 annihilation states

- Single vacancies 200 ps [1]
- Reduced-lattice ~ 10 ps
- ***Unidentified (X) defects (120-140 ps) ??***

Defects with free volumes smaller than V_1

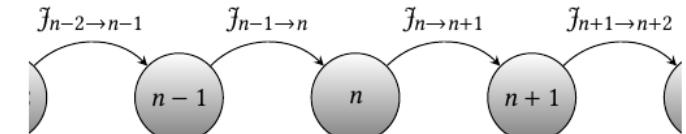
→ Oxygen –vacancy complexes, O_pV_1 ?

p	τ (ps)
1	170
2	142
3	143
4	130
5	124
6	132

?

- Mean field description of microstructure evolution, evolution of cluster concentrations C_n :

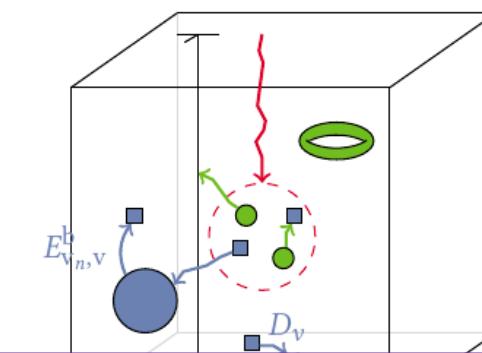
$$\frac{dC_n}{dt} = G_n + \underbrace{\sum_{m \in M} J_{n-m \rightarrow n}}_{\text{irradiation}} - \underbrace{\sum_{m \in M} J_{n \rightarrow n+m}}_{\text{association/dissociation}} - \underbrace{\sum_{m \in \Omega} J_{m \rightarrow m+n}}_{\text{sinks (ex.: dislocations)}} - k_{d,n}^2 D_n (C_n - C_n^e)$$



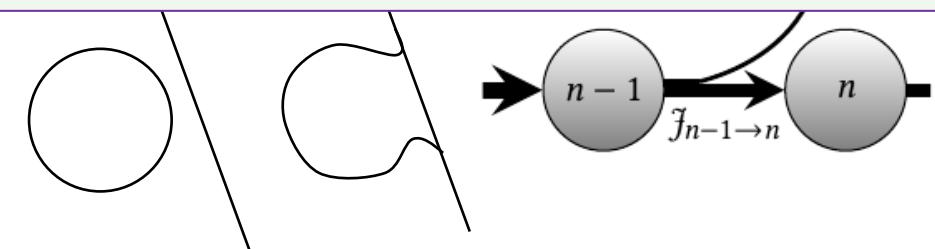
with

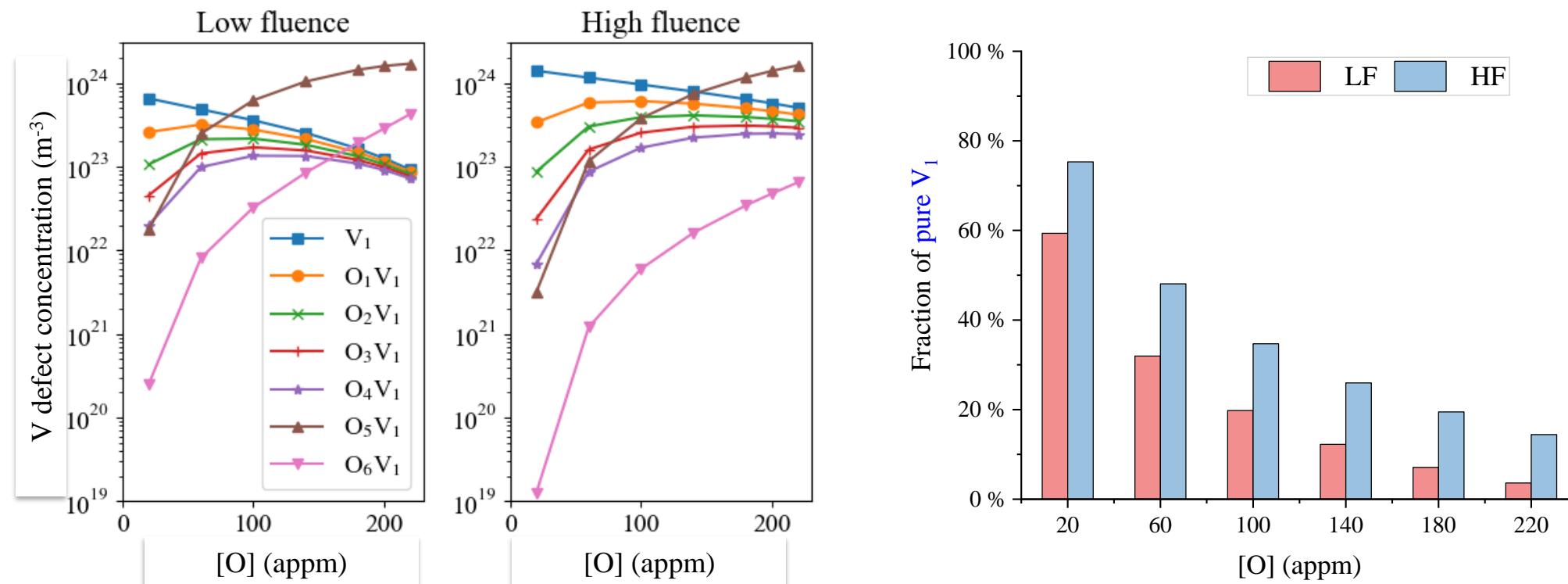
$$J_{n \rightarrow n+m} = \underbrace{\beta_{n,m} C_n C_m}_{\text{association}} - \underbrace{\alpha_{n+m,m} C_{n+m}}_{\text{dissociation}}$$

Sink strengths: $k_{n,m}^2 = \beta_{n,m} C_n / D_m$



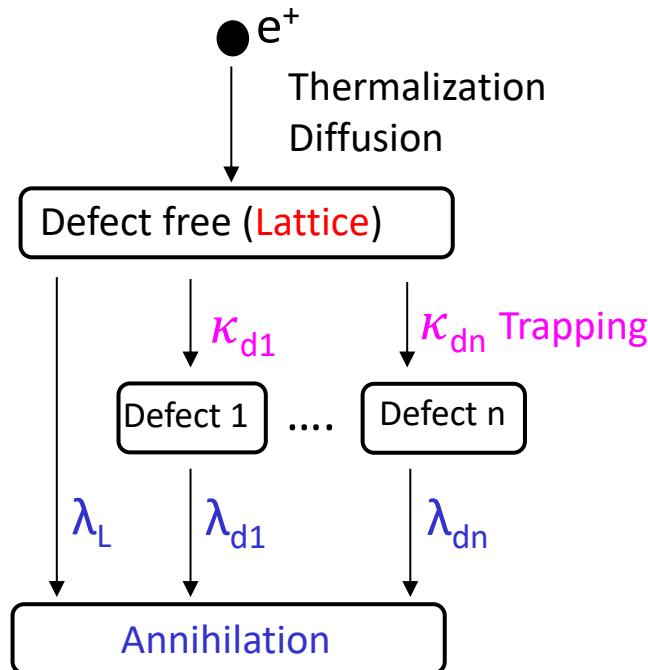
Defects (V_n , $SiAn$) evolution in matrix with O and without O





Concentration of **pure V_1** decreases with increasing of O, depends on fluence
→ **pure V_1** and **Oxygen-vacancy complexes (O_{1-6}V_1)** coexist

Assuming **n independent defects** and **no de-trapping** from defects [1]



Theoretical PALS(t)

$$1. PALS(t) = R(t) * \sum \left(\frac{I_{di}}{\tau_{di}} e^{-\frac{t}{\tau_{di}}} \right) + \frac{I_1}{\tau_1} e^{-\frac{t}{\tau_1}} + BG \quad R(t), BG: \text{experimental values}$$

τ_{di} ($1/\lambda_{di}$) calculated using TCDFT

$$I_{di} = \frac{k_{di}}{\lambda_L - \lambda_i + \sum k_{di}}, \text{ and } I_1 + \sum_{di} I_{di} = 1$$

I_{di} : Intensity of lifetime component d_i

Where trapping rate, $\kappa_{di} = c_{di} \cdot \mu_{di}$

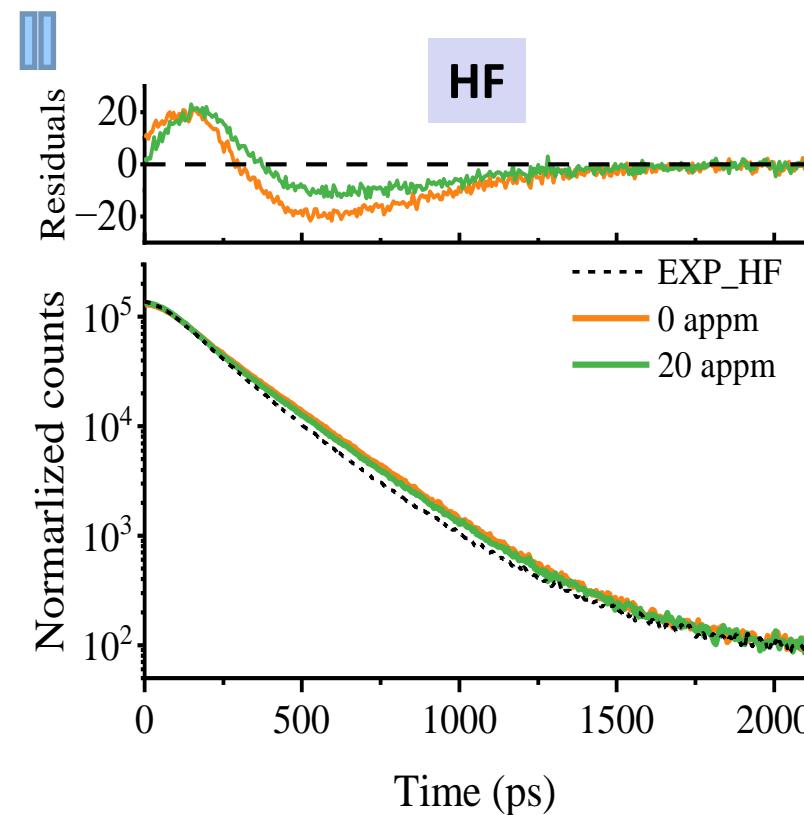
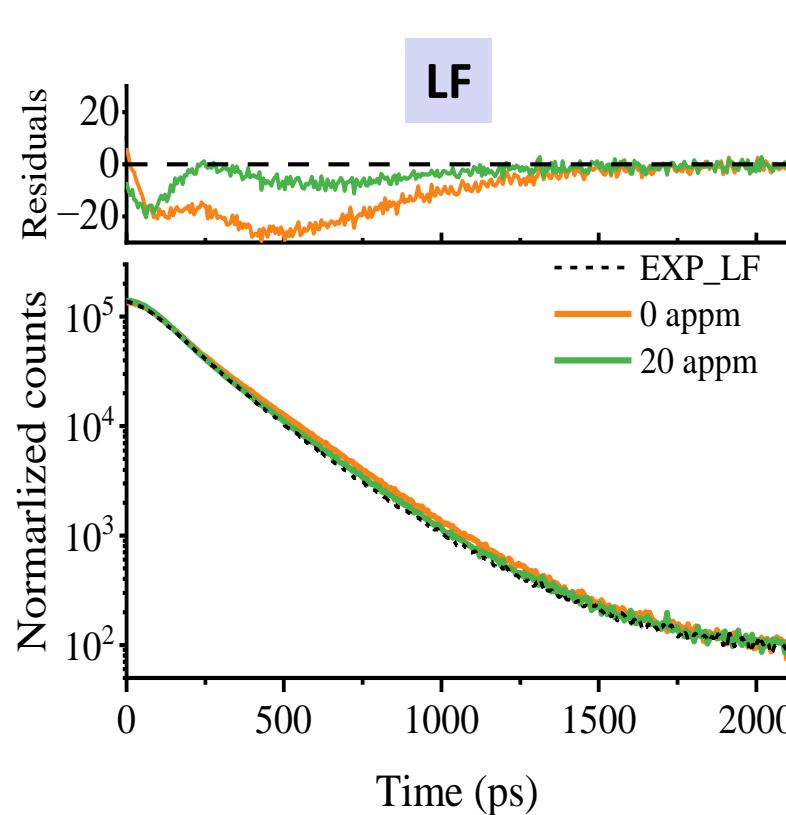
c_i : vacancy (V_i) concentration

μ_i : specific trapping coefficient

$$PALS(t) = R(t) * \sum \left(\frac{I_{di}}{\tau_{di}} e^{-\frac{t}{\tau_{di}}} \right) + \frac{I_1}{\tau_1} e^{-\frac{t}{\tau_1}} + BG$$



CD: Concentration
DFT: Lifetime



Trapping-model without O :

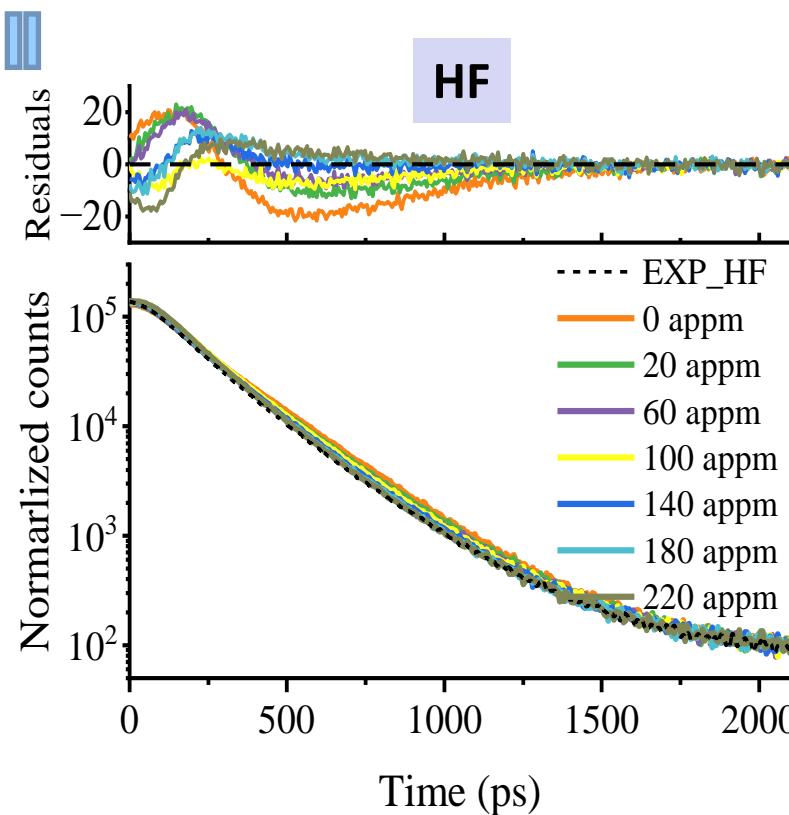
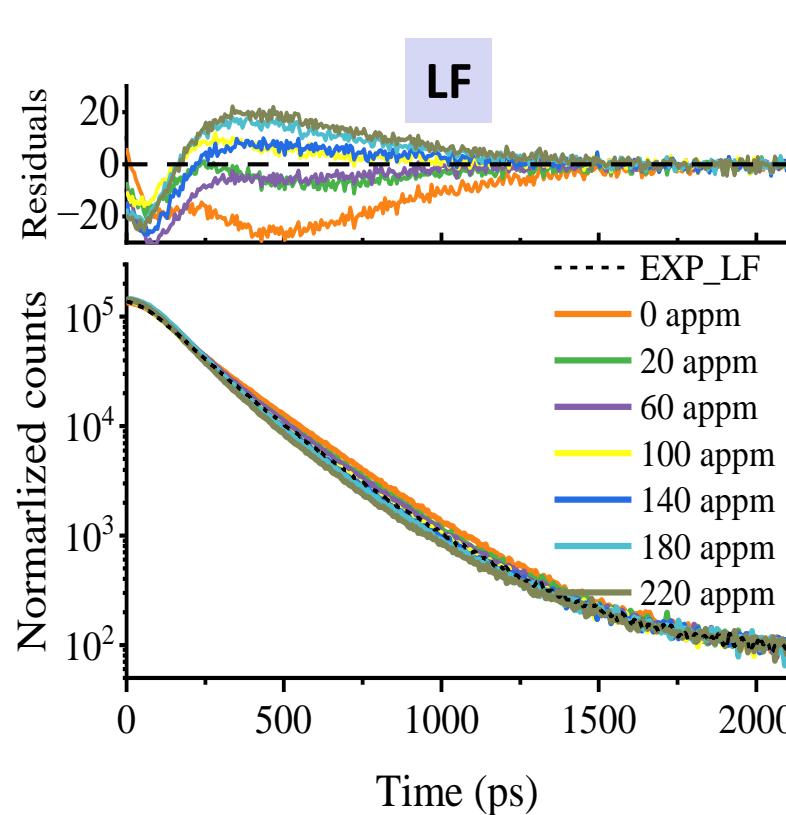
- $PALS(t)_{th} \neq PALS(t)_{Exp}$
→ Other defects

Trapping-model with O :
better agreement

$$PALS(t) = R(t) * \sum \left(\frac{I_{di}}{\tau_{di}} e^{-\frac{t}{\tau_{di}}} \right) + \frac{I_1}{\tau_1} e^{-\frac{t}{\tau_1}} + BG$$



CD: Concentration
DFT: Lifetime



Trapping-model without O :

- $PALS(t)_{th} \neq PALS(t)_{Exp}$
→ Other defects

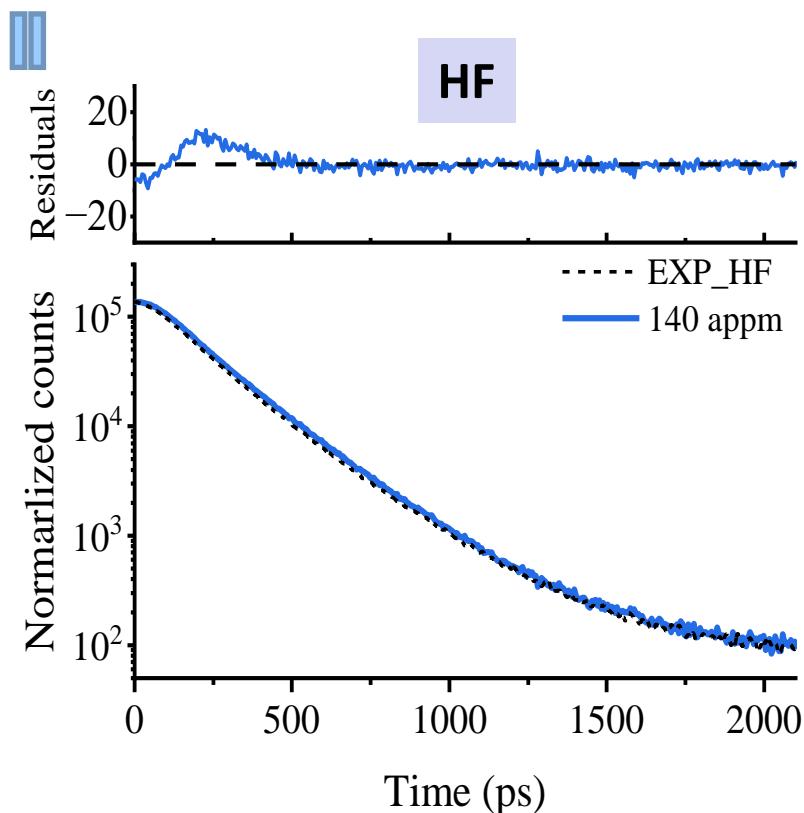
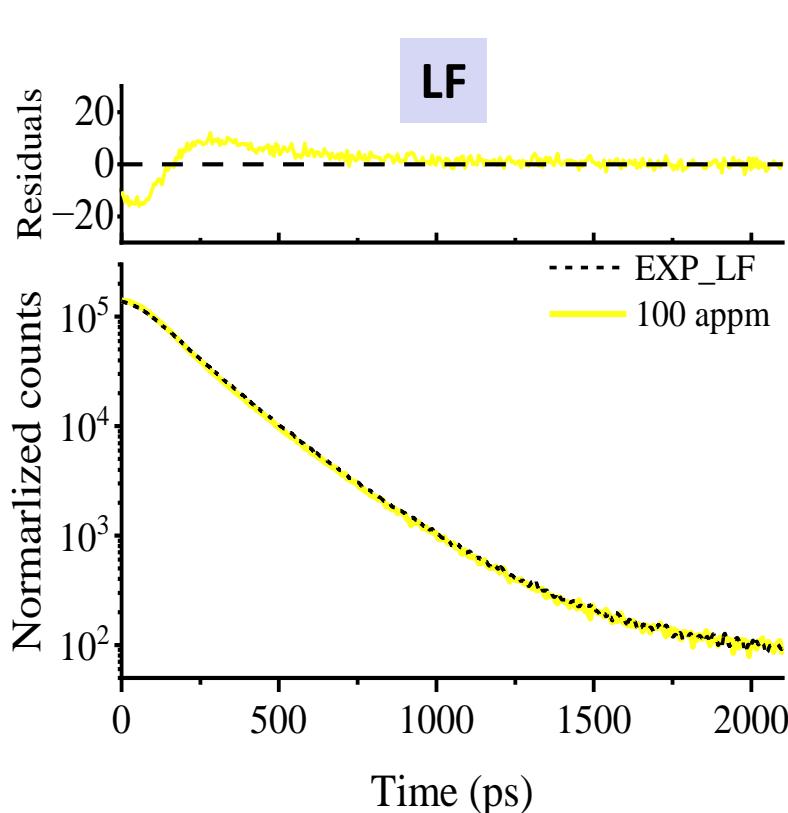
Trapping-model with O :

- $PALS(t)_{th} \approx PALS(t)_{Exp}$

$$PALS(t) = R(t) * \sum \left(\frac{I_{di}}{\tau_{di}} e^{-\frac{t}{\tau_{di}}} \right) + \frac{I_1}{\tau_1} e^{-\frac{t}{\tau_1}} + BG$$



CD: Concentration
DFT: Lifetime



Trapping-model without O :

- $PALS(t)_{th} \neq PALS(t)_{Exp}$
→ Other defects

Trapping-model with O :

- $PALS(t)_{th} \approx PALS(t)_{Exp}$
- ✓ LF: 100 appm O
- ✓ HF: 100-180 appm O

→ Agree with SIMS:

$$[O] = 30-250 \text{ appm}$$

→ X defects = mix of $O_p V_1$

✓ 2 illustrations

- Oxygen vacancy interactions
- Vacancy clusters distribution in self-irradiated tungsten

New methodology

New insight into quantifying vacancy distribution in self-ion irradiated tungsten: a combined experimental and computational study

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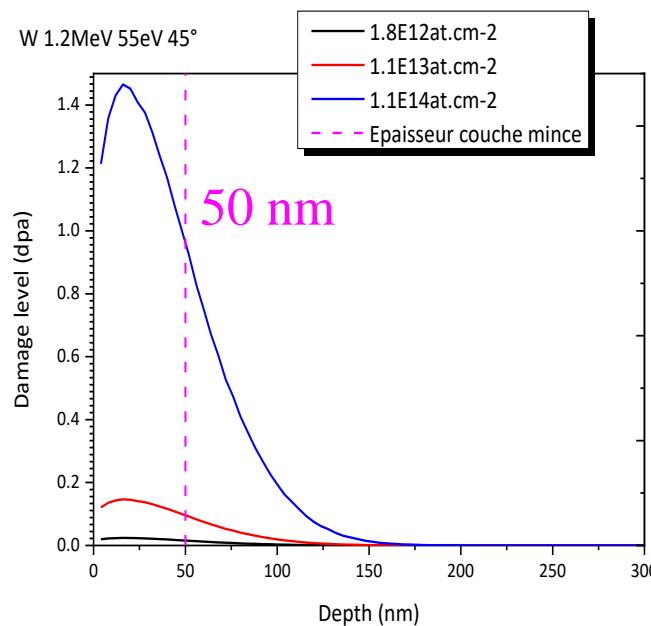
Accepted in

NANO LETTERS

Irradiation with W ions, SRIM calculations (KP)

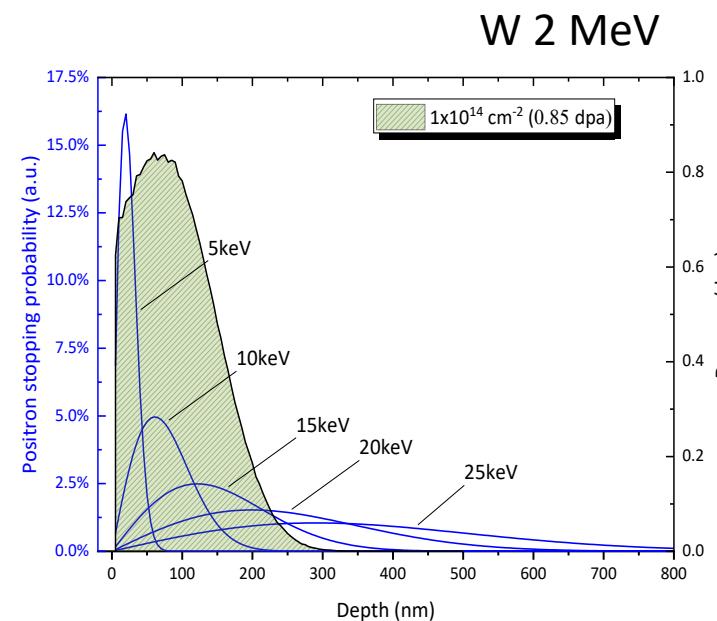
Before irradiation : Annealing at 1600°C/1H/Vacuum

- 1.2 MeV in thin and thick samples:

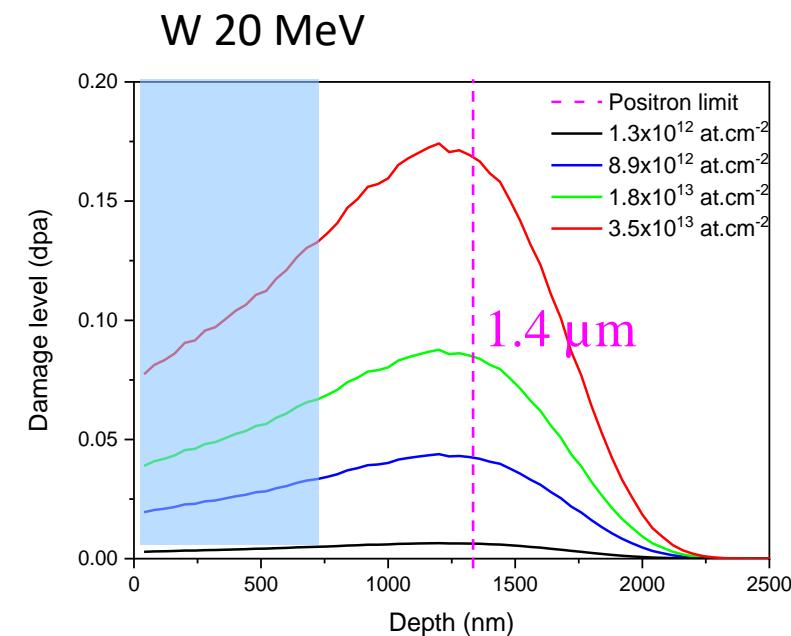


Dpa* : mean dpa value in the thin foil

- 2 or 20 MeV in thick samples:



Dpa* : at the mximum of the peak



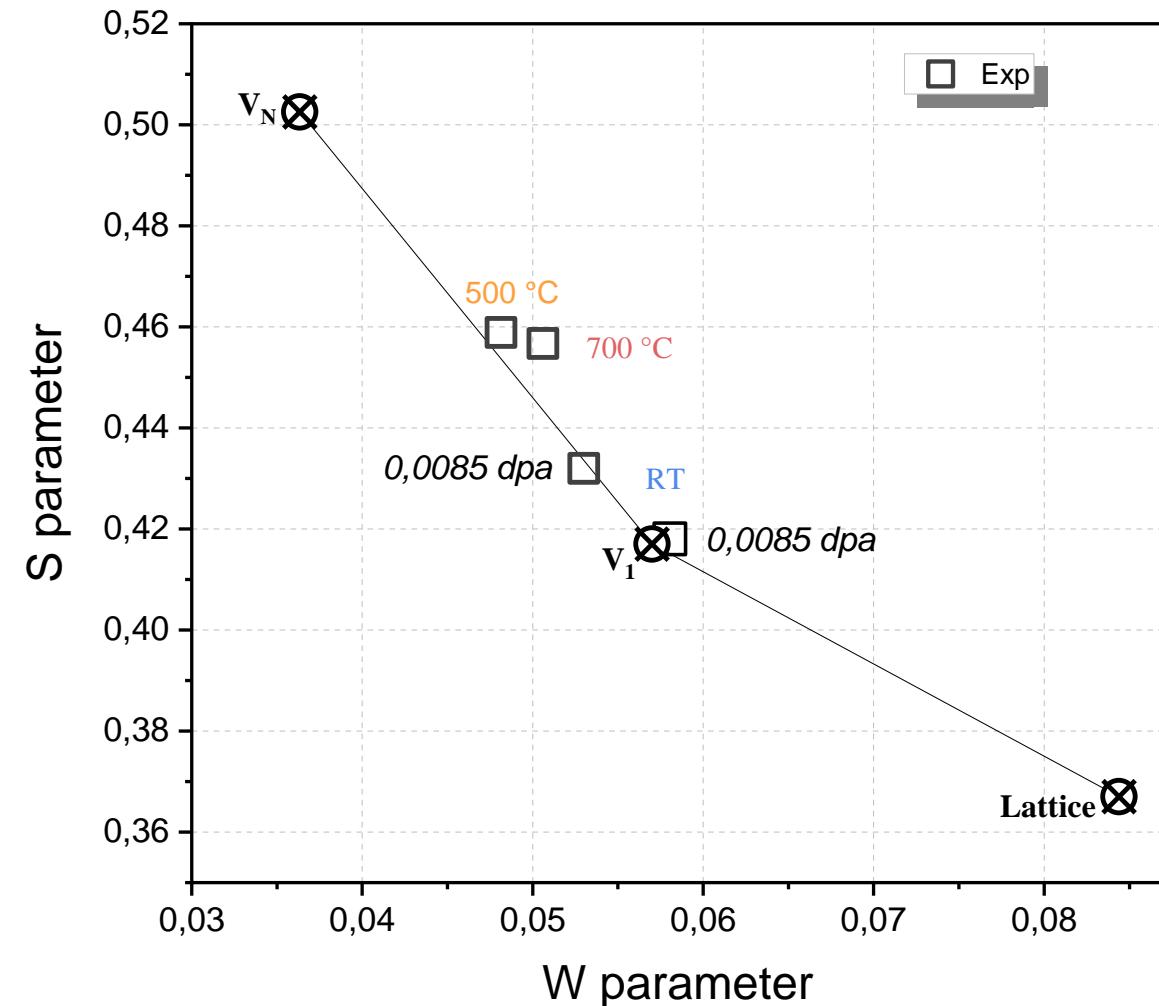
Dpa* : mean dpa value in 700nm surface region,

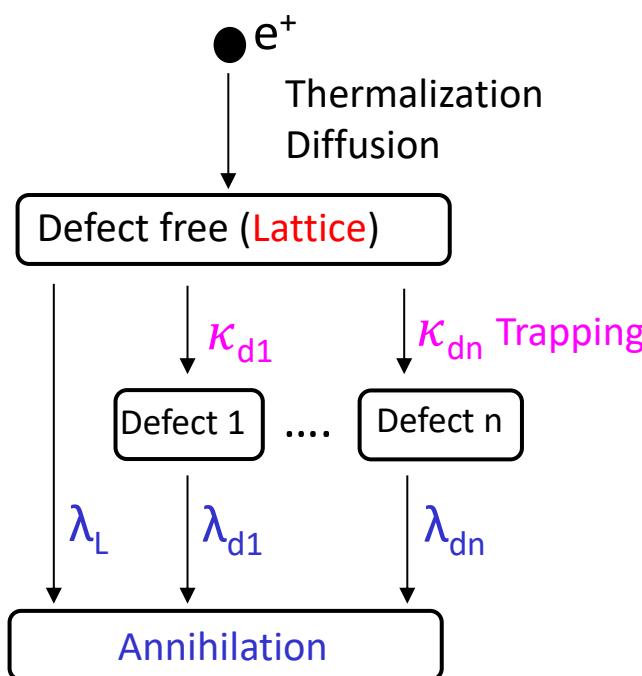
post-mortem characterizations : PAS (with slow positron beam, S(E) & W(E)) and TEM

Ion energy (MeV)	dpa	Temp (°C)	W	S
[1] 2	0.0085 (peak)	RT	0.058(1)	0.418(1)
	0.085 (peak)		0.053(1)	0.432(1)
[2] 20	0.02 (mean 0- 700 nm)	500 700	0.0481(1)	0.459(2)
			0.051(1)	0.457(4)

[1] Mean value of 5 fits

What is the distribution of Vacancy defects ?





$$\begin{cases} S = S_L \cdot f_L + \sum S_{di} \cdot f_{di} \\ W = W_L \cdot f_L + \sum W_{di} \cdot f_{di} \end{cases}$$

S_i and W_i calculated using TCDFT

f_{di} : Fraction of annihilation state d_i

Assuming **n independent defects** and **no de-trapping** from defects [1]

Total trapping, $f_L = 0$ and $\kappa_{di} \gg \lambda_L - \lambda_{dn}$

$$\Rightarrow f_1 = \frac{\kappa_{d1}}{\kappa_{d1} + \dots + \kappa_{dn}} \dots f_{dn} = \frac{\kappa_{dn}}{\kappa_{d1} + \dots + \kappa_{dn}}$$

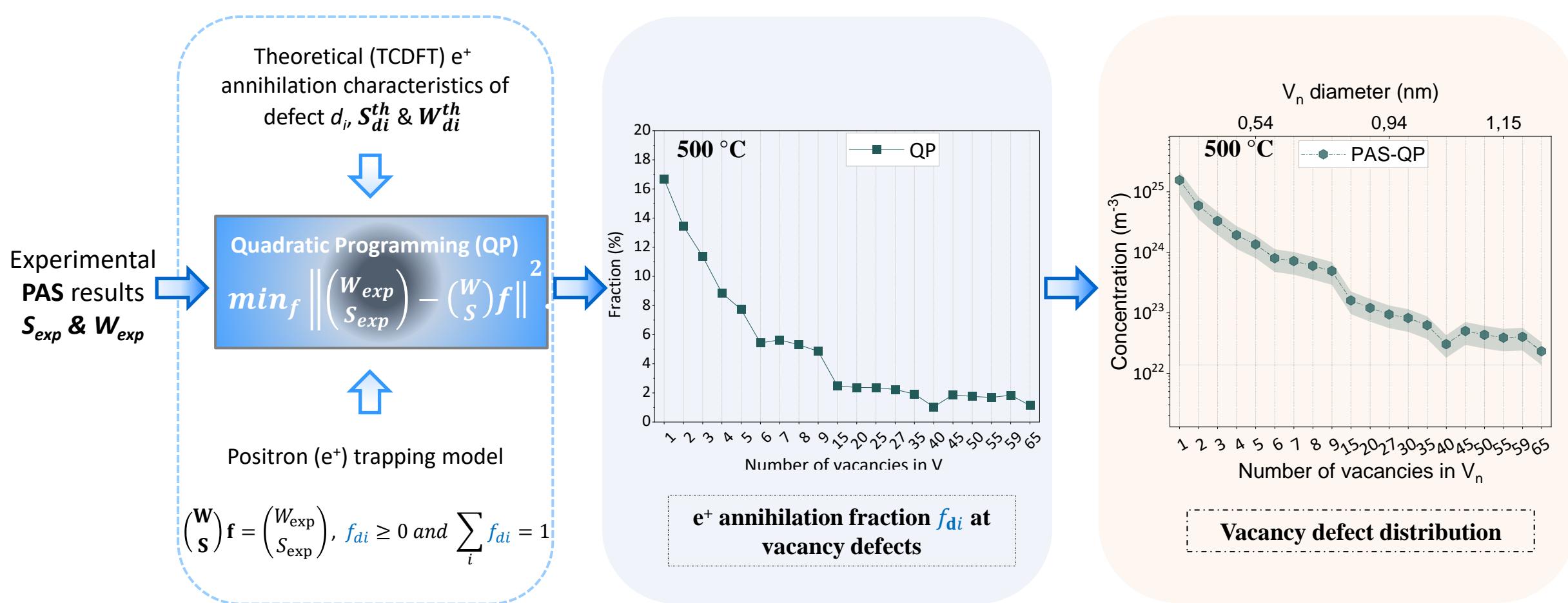
$$\text{and } f_L + \sum_{d_1} f_{di} = 1$$

Where trapping rate, $\kappa_{di} = C_{di} \cdot \mu_{di}$

C_{di} : vacancy (V_i) concentration

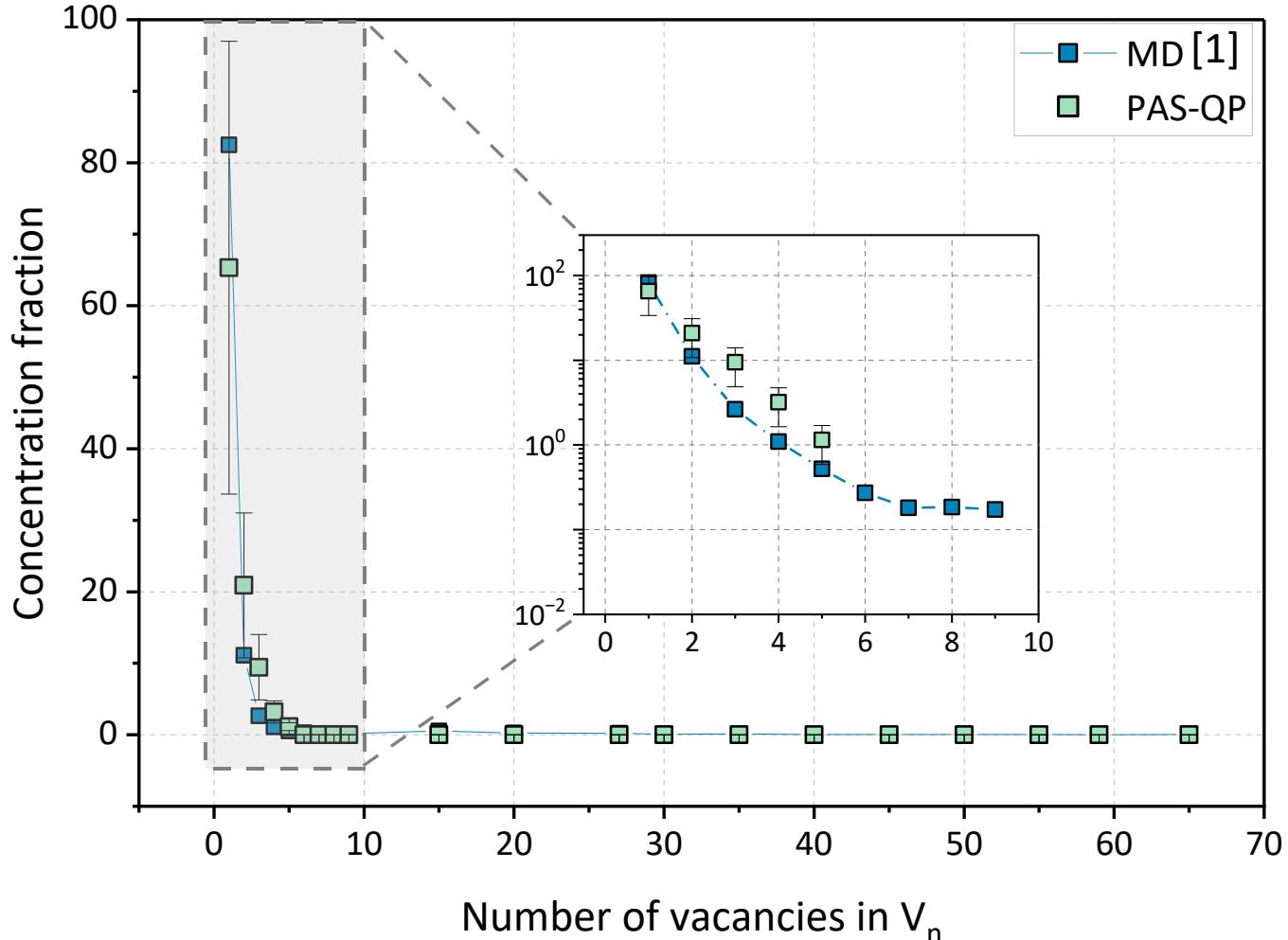
μ_{di} : specific trapping coefficient

If d_i is a vacancy cluster V_i



QP preset : **only V_n** with $n=1-65$

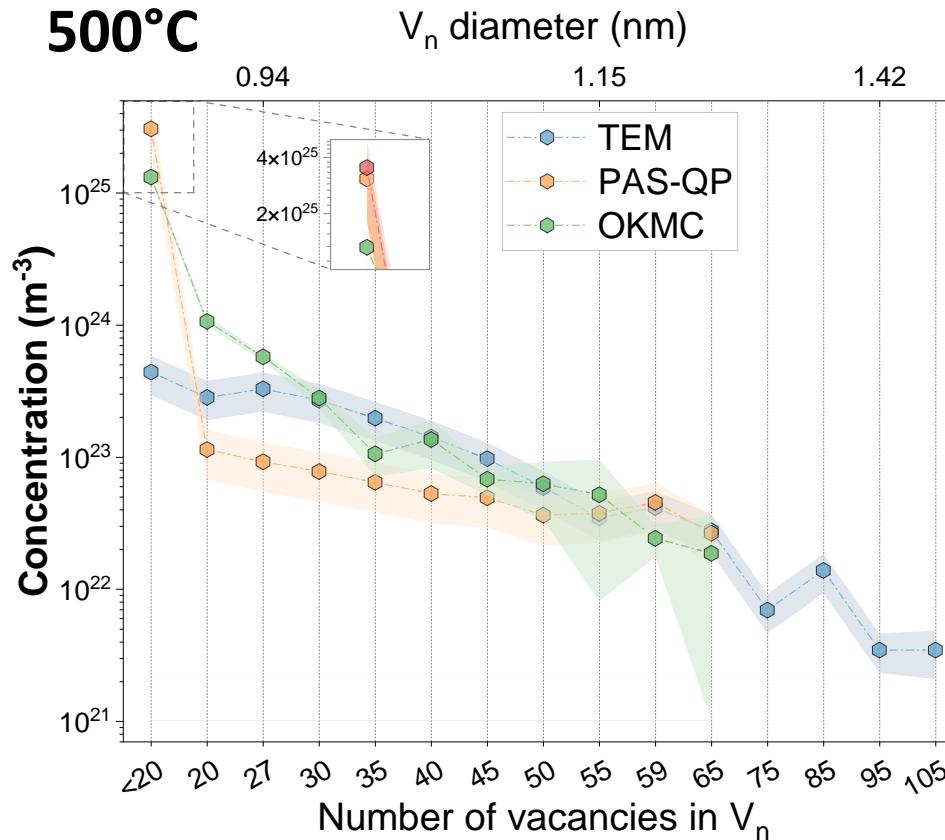
self-irradiated Tungsten at 0,085 dpa and RT



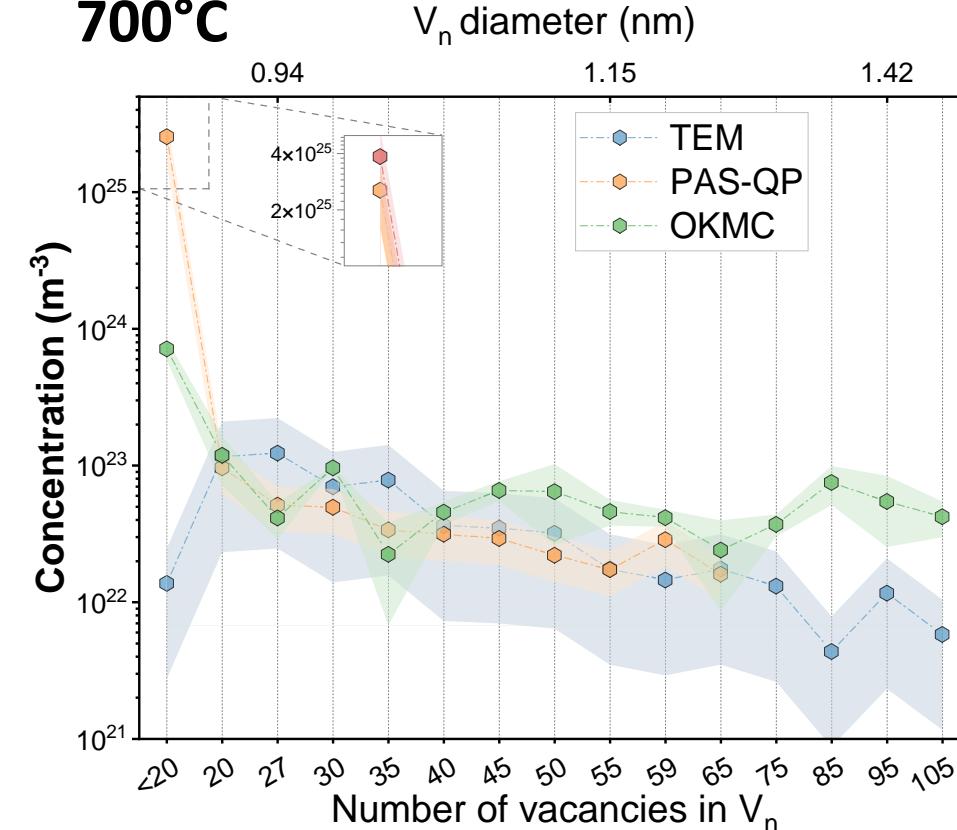
Very close distributions for PAS and MD

QP preset : **only** V_n with $n=1-65$

500°C



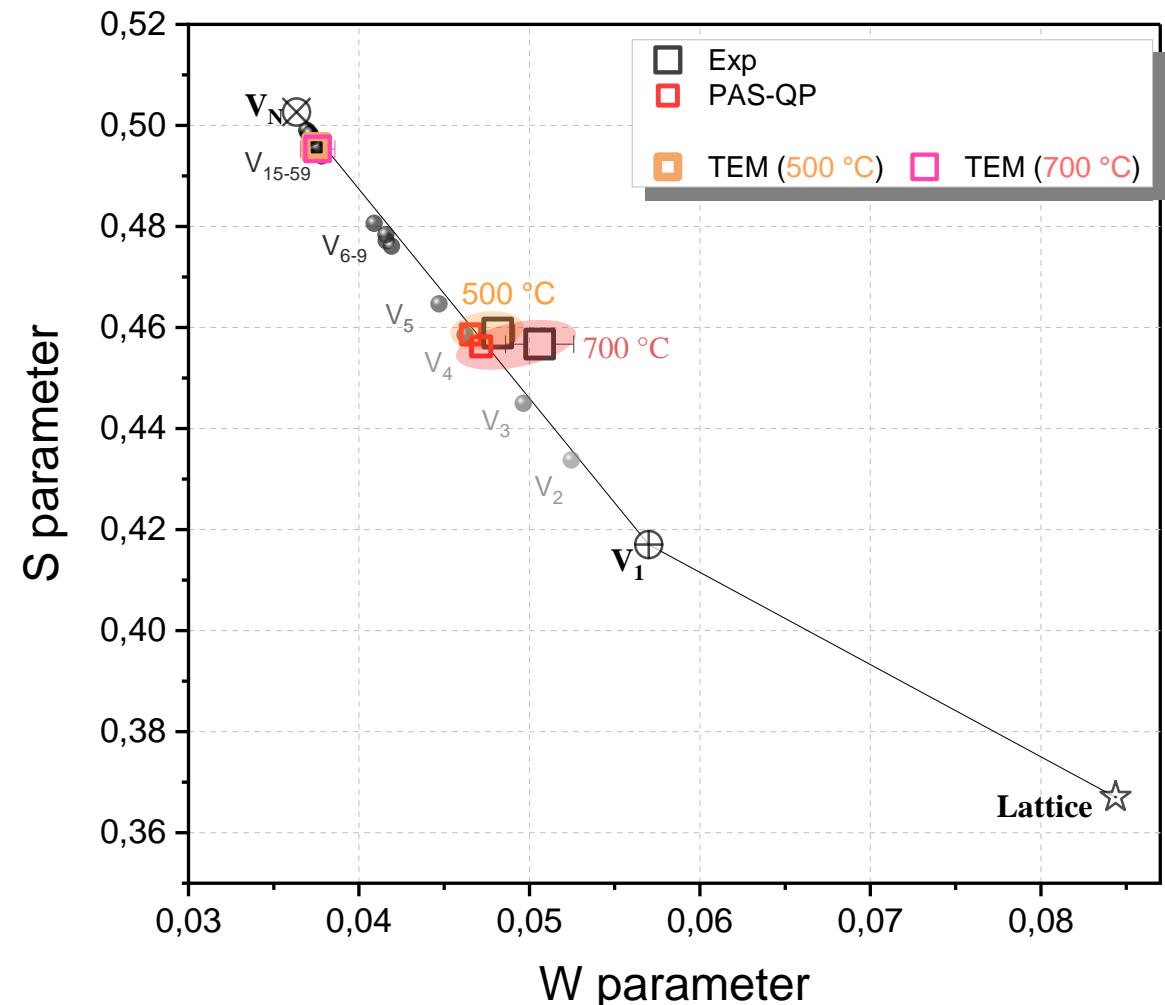
700°C



More small vacancy defects (V_n , $n<20$) in PAS than in TEM (due to detection limit)
OKMC (MMonCa [1]) predicts a large fraction of small vacancy defects (V_n , $n<20$)

- The large difference between S & W calculated from TEM Vn distribution confirms the presence of small vacancy clusters that can not be quantified using TEM.
- The S & W points calculated from the Vn distribution extracted using QP (red squares) are on the left of the Experimental data (black squares).
- Positrons annihilate in a defect different from the Vn ($n=1-65$) clusters and with a larger W value.

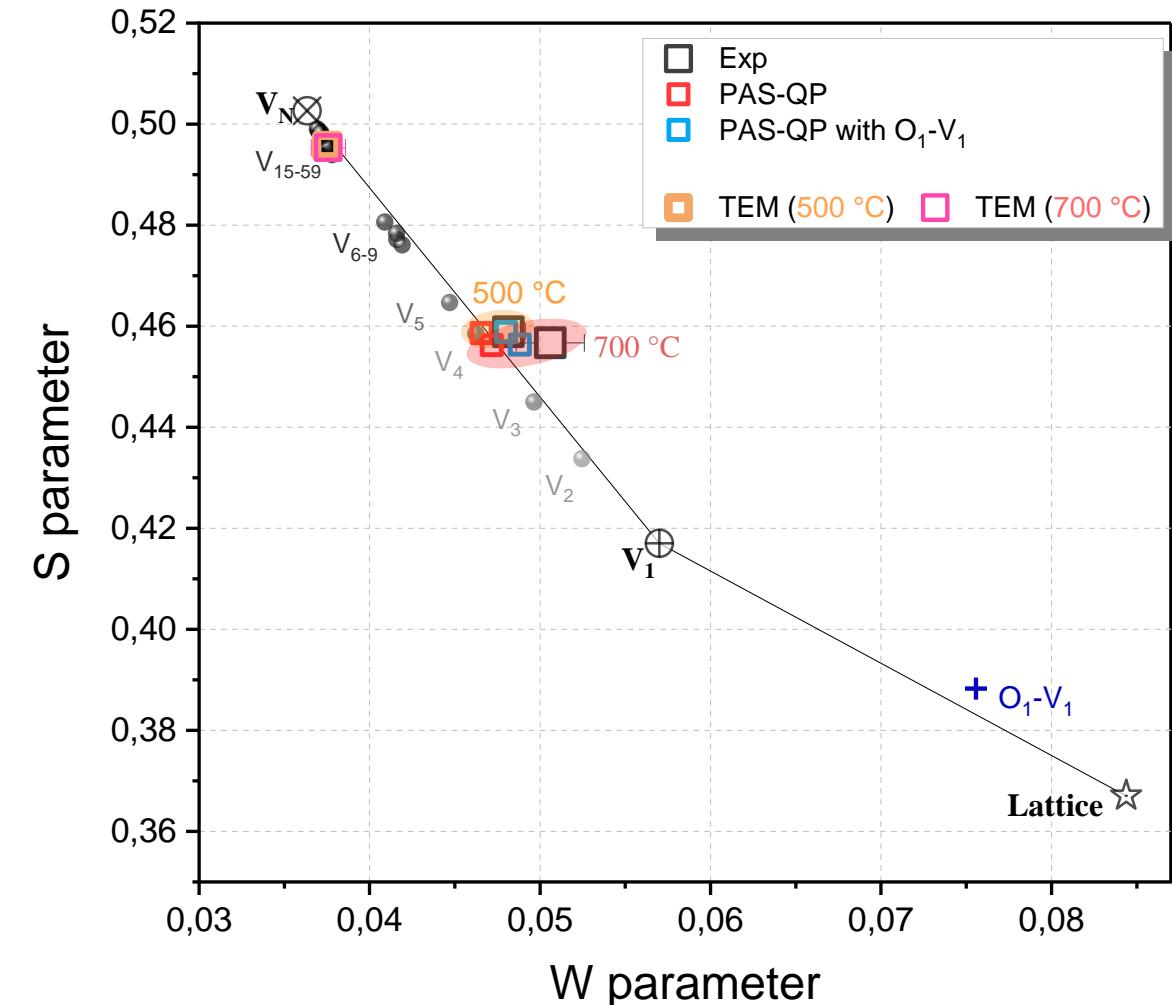
Oxygen vacancy complexes ?



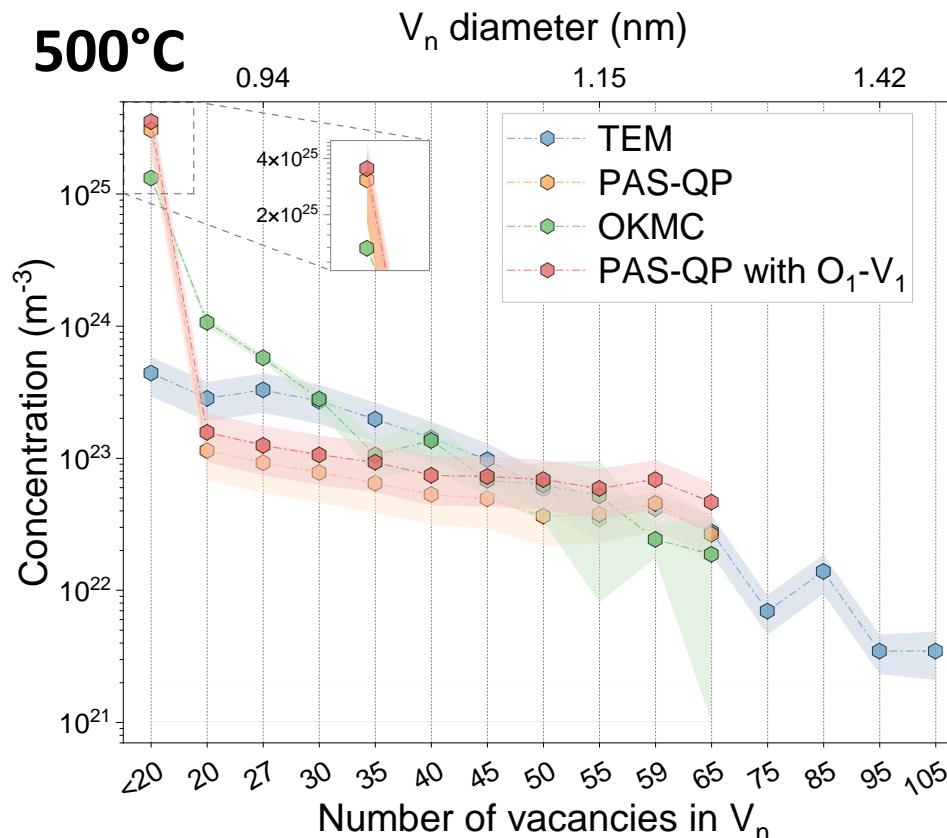
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Oxygen vacancy complexes ?

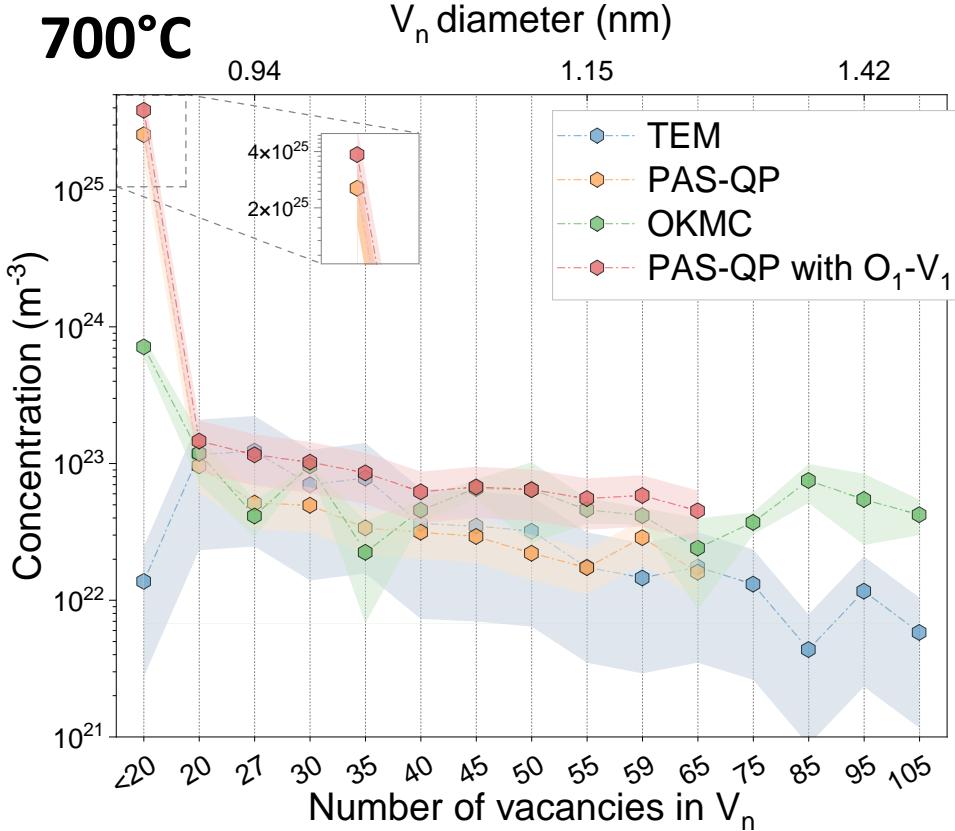
The agreement becomes better when O₁-V₁ complexe is introduced in the QP model



QP preset : V_n with $n=1-65 + O_1-V_1$



self-irradiated Tungsten at 0,0085 dpa and RT



- With O_1-V_1 , concentration of vacancy clusters **increases**
- Swelling deduced from PAS is higher than from TEM

Swelling (%)

	500°C	700°C
TEM	0.09 (± 0.02) %	0.04 (± 0.02) %
PAS	0.6 (± 0.3) %	0.6 (± 0.5) %

- Positron Lifetime (PALS) and Doppler Broadening (DB) spectrometry
- Theoretical annihilation characteristics τ, S, W of defects
- Trapping model
- Quadratic Processing
 - Experimental confirmation of strong interaction between Oxygen and vacancy in tungsten :
 - Oxygen-vacancy complexes are formed
 - The Oxygen effect has to be taken into account in modelling*
 - Distribution of vacancy defects in self-irradiated tungsten
 - Small vacancy clusters are highlighted and can be quantified
 - **Data to parametrize and validate models**



Z Hu, M Sidibe, C. Genevois, P. Desgardin, J. Joseph

TEM, DB PAS

Q Yang (phD), P. Olsson



I Makkonen



DFT calculations (PAS)

T Jourdan



Cluster dynamics

J Wu (phD), F. Granberg



MD, OKMC, ??? calculations



B. Décamps, C. Baumier, Accelerator Team
M. Loyer-Prost, E. Bordas



R. Schaublin



And contributions from



Thank you for your attention